

Structural dynamics in atomic wire systems at surfaces studied by ultrafast-electron diffraction: Excitation, metastable states and relaxation

T. Frigge, B. Hafke, T. Witte, B. Krenzer, C. Brand, J. Fortmann, T. Groven, M. Tajik, D. Janoschka, P. Dreher, F.J. Meyer zu Heringdorf, C. Streubühr, A. Samad Syed, V. Mikšić Trontl, I. Avigo, P. Zhou, M. Ligges, D. von der Linde, U. Bovensiepen, S. Wippermann¹⁾, A. Lücke²⁾, S. Sanna²⁾, U. Gerstmann²⁾, W. G. Schmidt²⁾,

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Experimental Physics
University of Duisburg-Essen
Germany

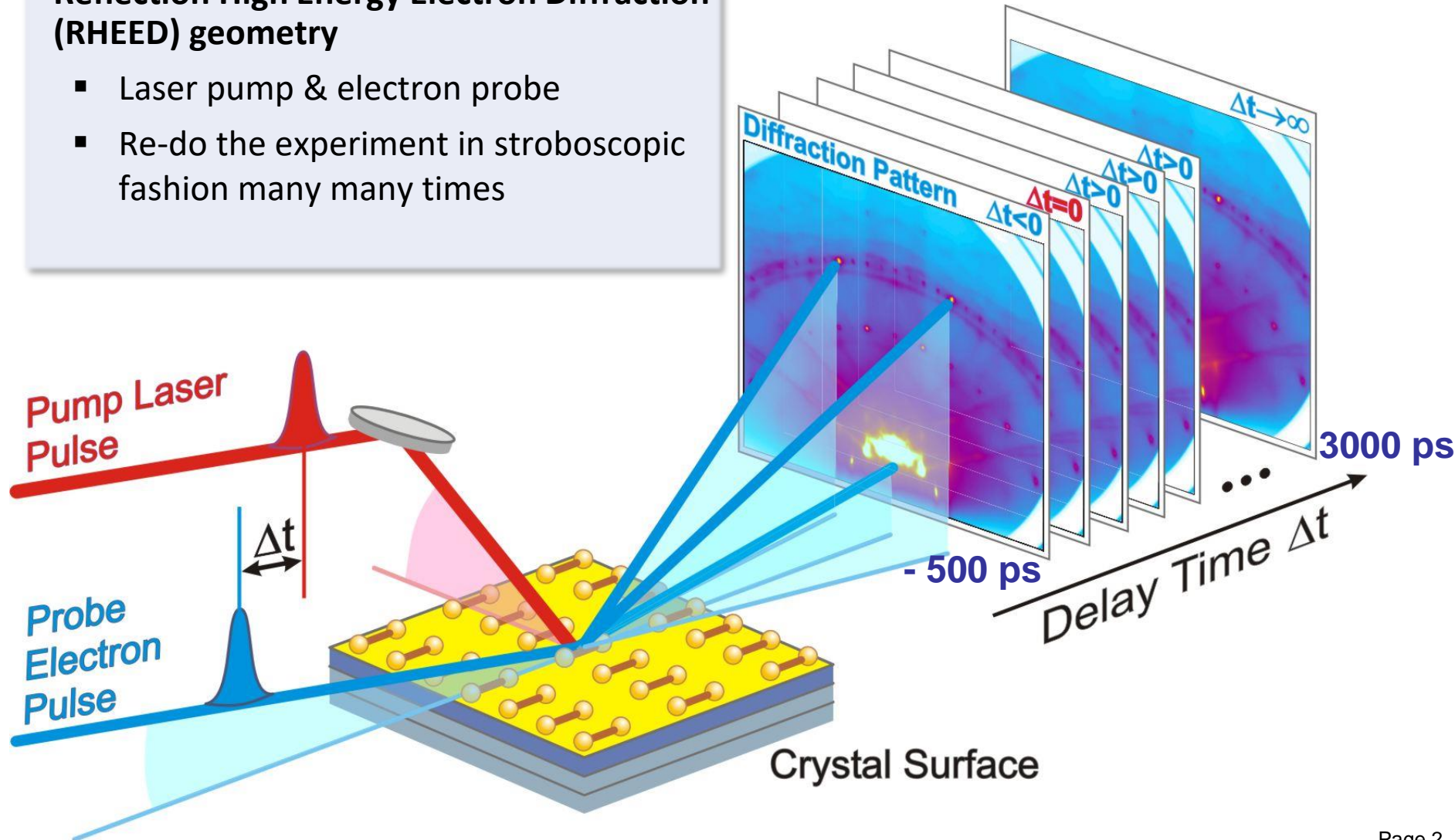
¹⁾ MPI Eisenforschung, Düsseldorf, Germany

²⁾ University of Paderborn, Germany

TR-RHEED in pump-probe setup

Time resolved diffraction at surfaces in Reflection High Energy Electron Diffraction (RHEED) geometry

- Laser pump & electron probe
- Re-do the experiment in stroboscopic fashion many many times



Electron scattering cross section
 $10^4 \dots 10^6$ larger than x-ray

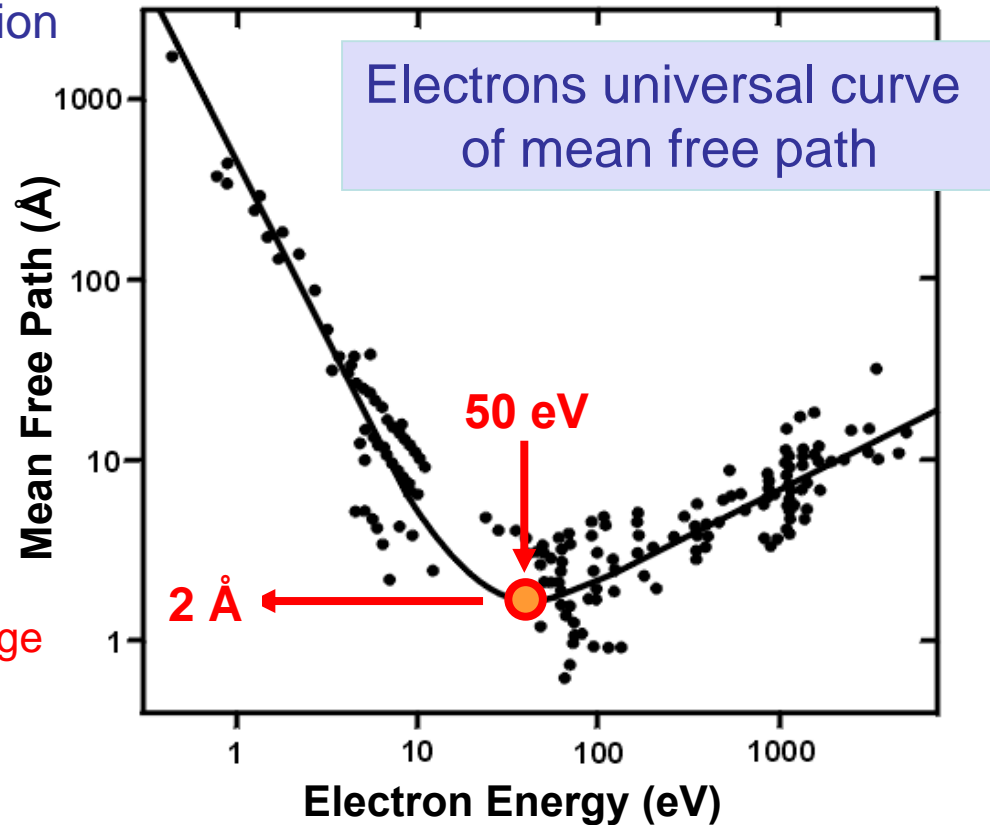
- dominant multiple scattering
- => no simple IV-analysis

LEED

- extrem surface sensitivity
- normal incidence
- no distortion of pattern
- **miniaturize setup to avoid huge temporal broadening of ns**

Science **345**, 200 (2014)
M.Gulde, S. Schäfer, C. Ropers

Nature Physics **14**, 184 (2018)
S. Vogelgesang, G. Storeck, J.G. Horstmann, T. Diekmann, M. Sivilis,
S. Schramm, K. Rossnagel, S. Schäfer, C. Ropers



Electron scattering cross section
 $10^4 \dots 10^6$ larger than x-ray

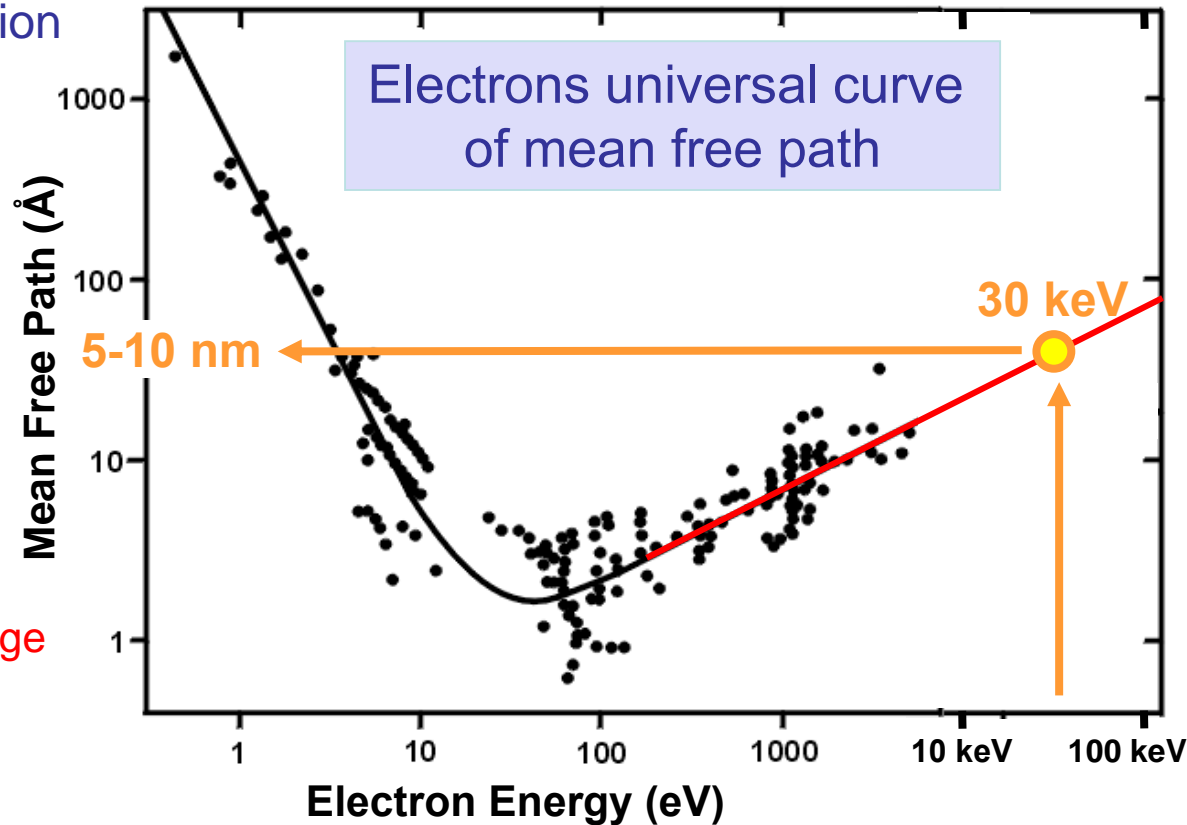
- dominant multiple scattering
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LEED

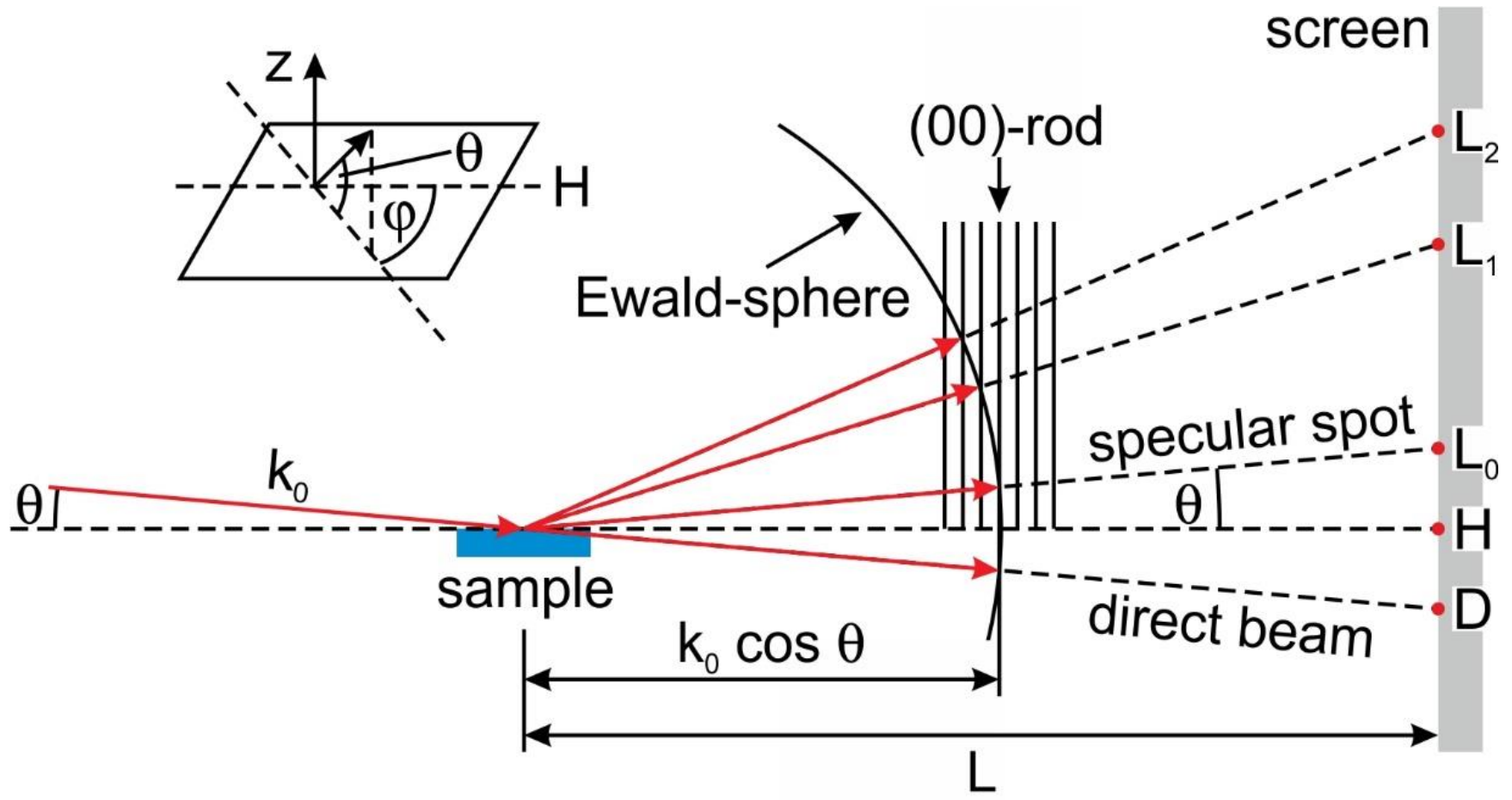
- extrem surface sensitivity
- normal incidence
- no distortion of pattern
- **miniaturize setup to avoid huge temporal broadening of ns**

=> RHEED @ 30 keV

- minimum temporal broadening < ps
- grazing incidence $2^\circ - 6^\circ$ for surface sensitivity
- distortion of pattern



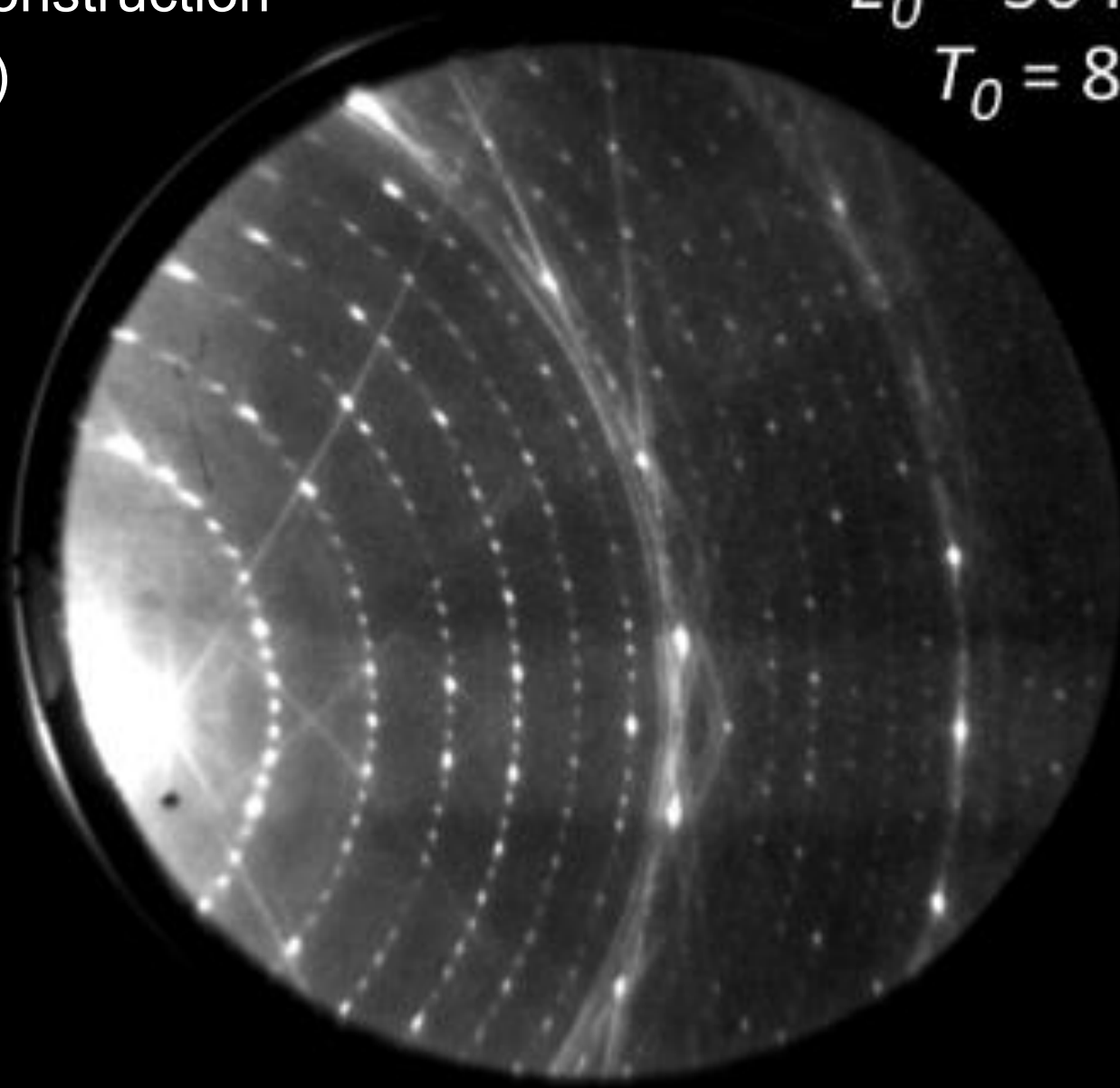
Curved Ewald sphere !



Curved Ewlad sphere !

(7x7) reconstruction
of Si(111)

$E_0 = 30 \text{ keV}$
 $T_0 = 80 \text{ K}$



fs Laser Pulses

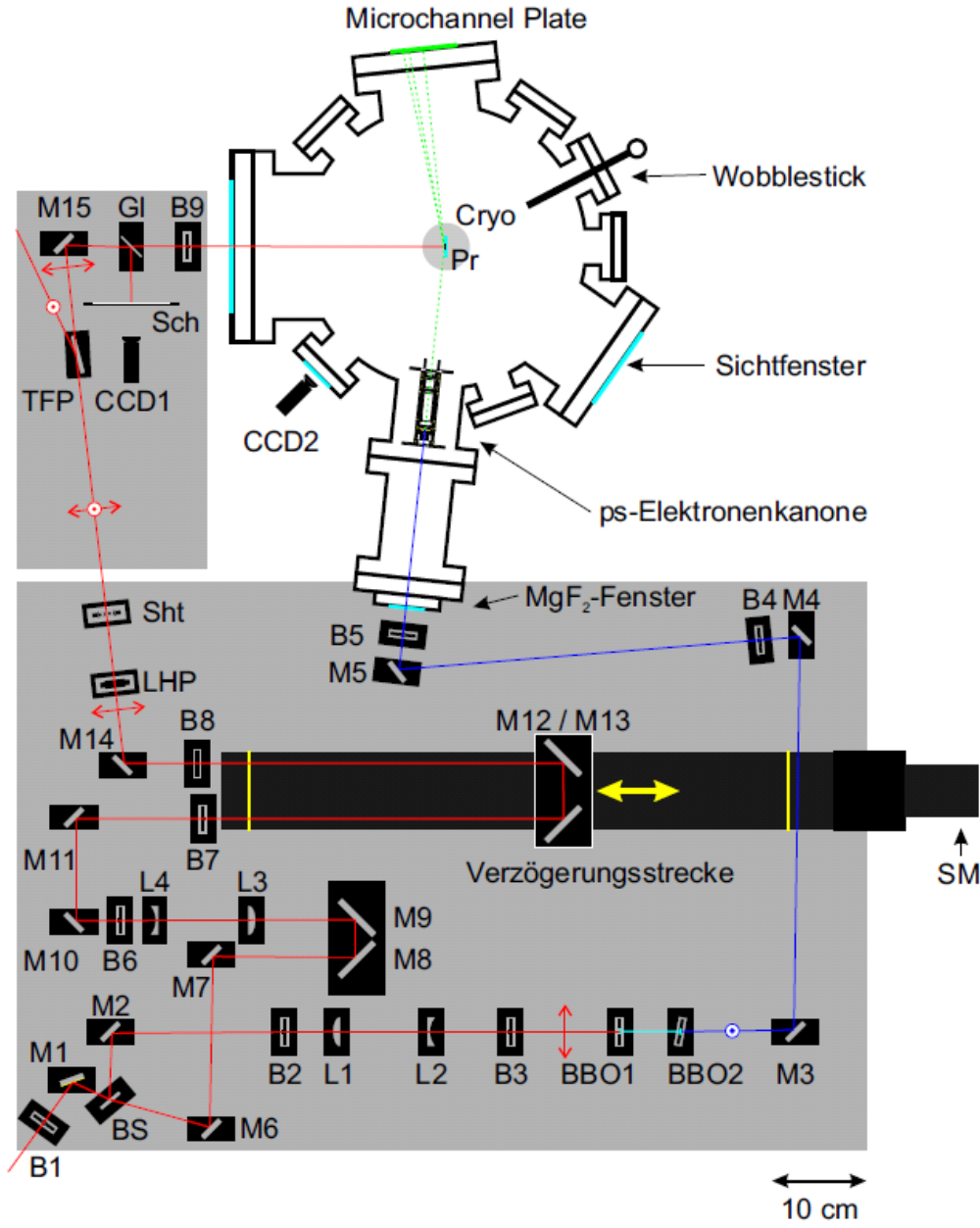
- Ti-Sapphire amplifier system
- $\lambda = 800 \text{ nm}$, $\hbar\omega = 1.55 \text{ eV}$
- 80 fs, 1 mJ per pulse @ 5 kHz
- fluence of up to 15 mJ/cm^2

UHV-System

- pressure $p = 1 \times 10^{-10} \text{ mbar}$
- sample 30 K – 1200 °C
- in-situ deposition of In, Bi, Pb ...

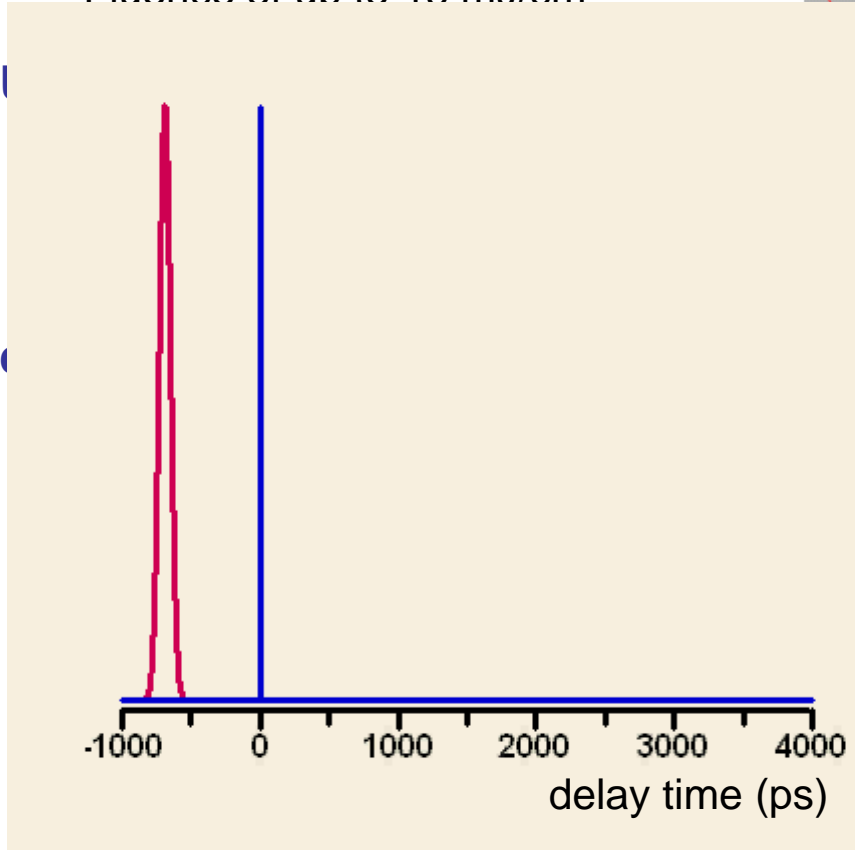
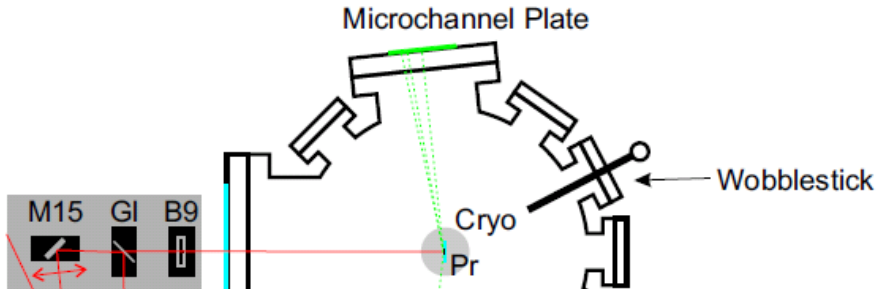
e-Diffraction

- RHEED 7 – 30 keV
- grazing incidence $2^\circ - 6^\circ$
- vertical momentum transfer $\Delta k_{\perp} = 4 - 20 \text{ \AA}^{-1}$
=> significant Debye-Waller effect
- reversible surface / film system
=> robust systems without radiation damage! More than 10^7 laserpulses per experiment

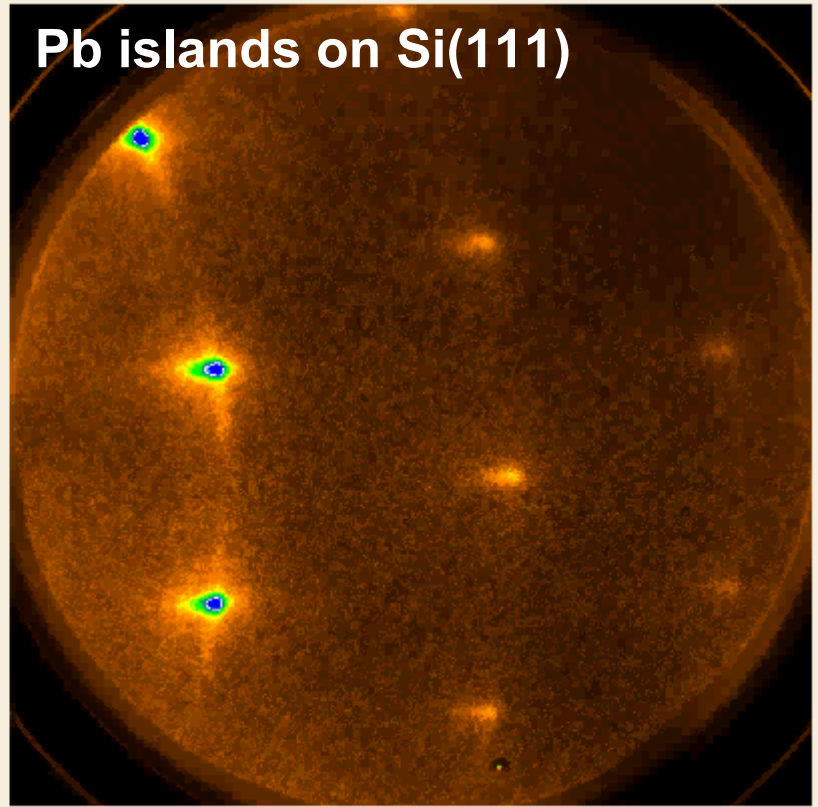


fs Laser Pulses

- Ti-Sapphire amplifier system
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- 80 fs, 1 mJ per pulse @ 5 kHz
- Fluence of up to 15 mJ/cm^2



per experiment

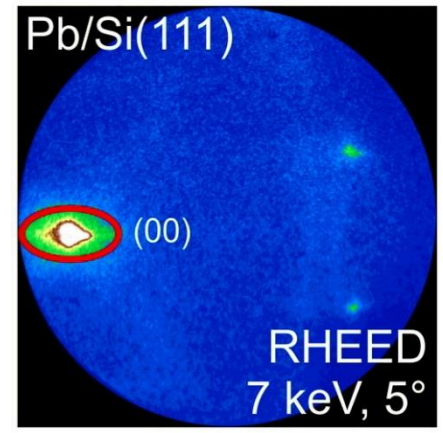
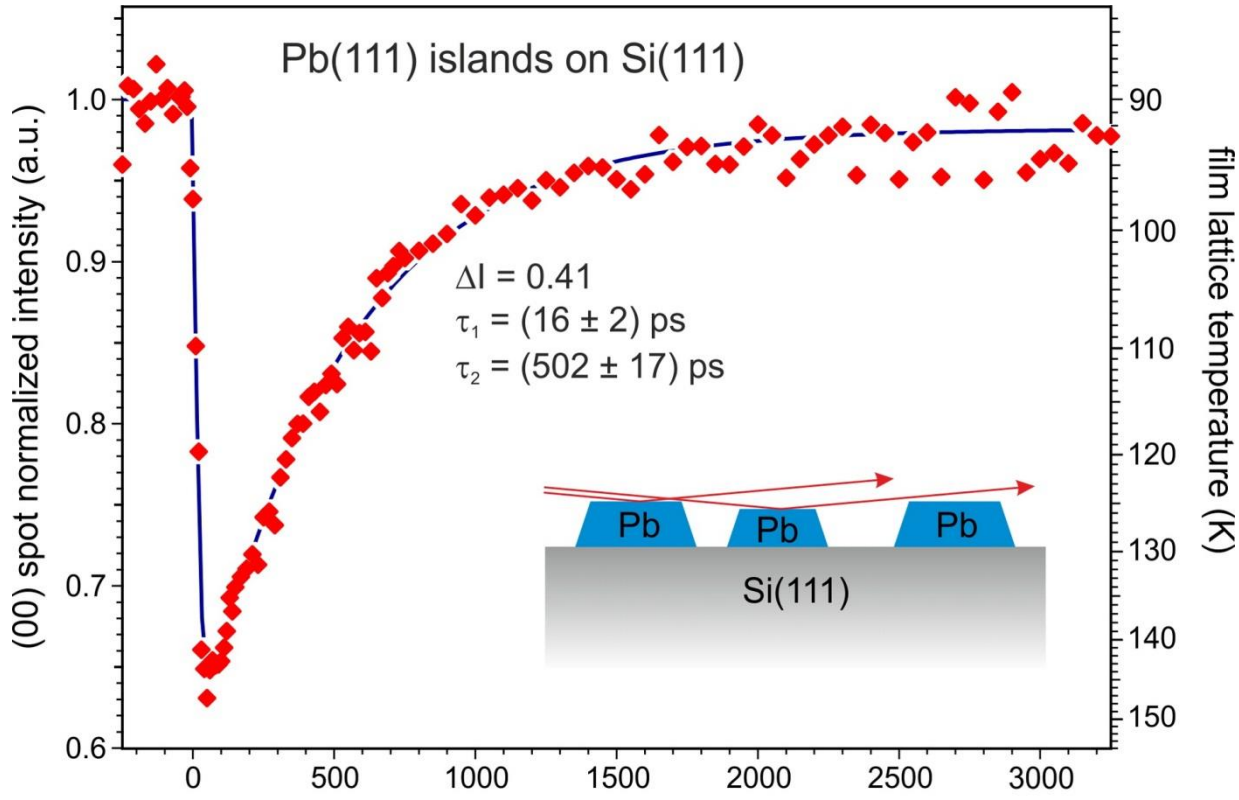


10 cm

Debye Waller effect $I/I_0 = \exp -1/3 \langle u^2 k^2 \rangle$

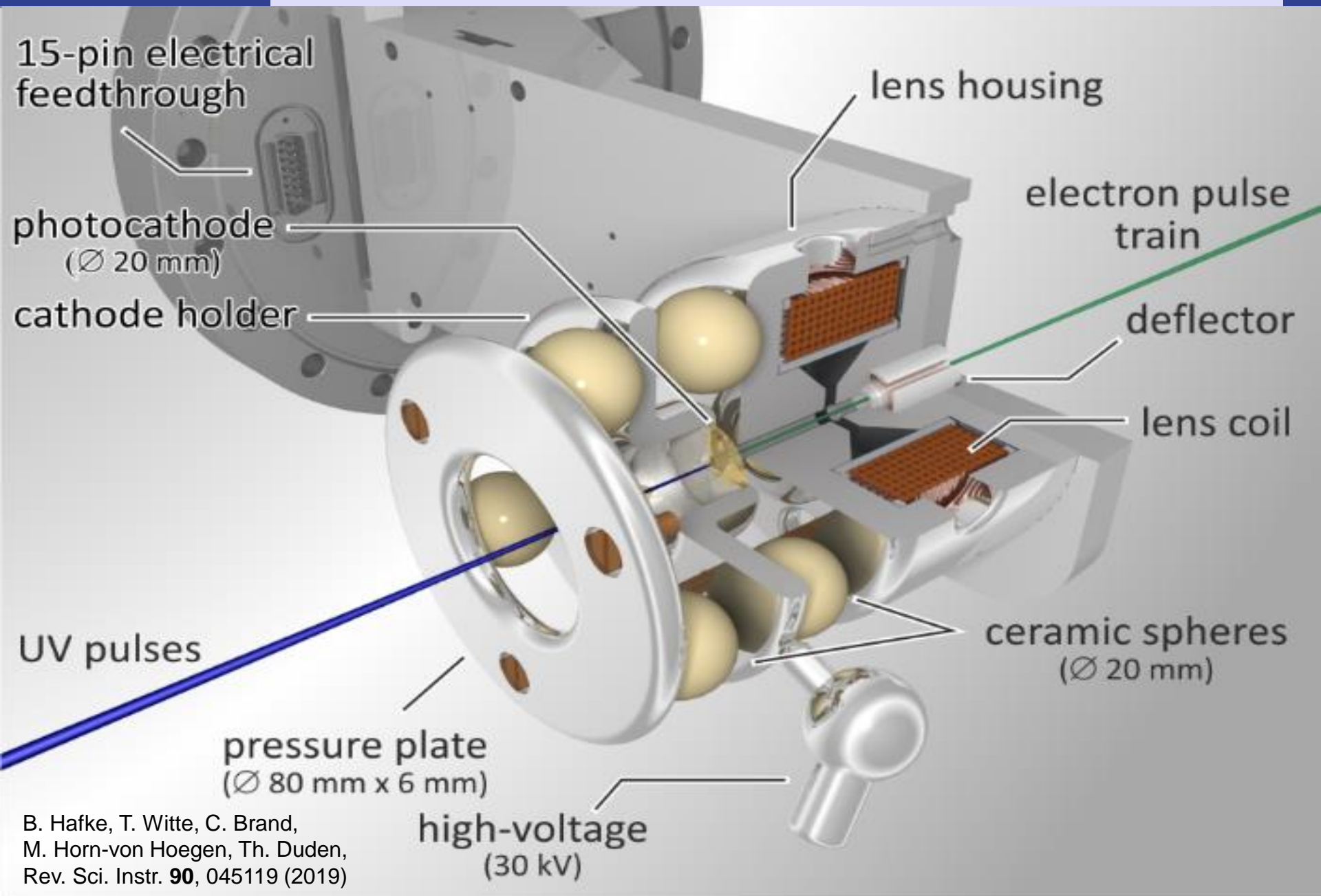
Cooling on the Nanoscale: 6 nm thick Pb(111) islands on Si(111)

Dominated by total internal reflection of phonons at Pb/Si interface: „heat is trapped in film“



A. Janzen et al., Surf. Sci. **600**, 4094 (2006) time delay (ps)
 B. Krenzer, A. Janzen, M. Horn-von Hoegen et al., New J. Phys. **8**, 190 (2006)
 A. Hanisch, B. Krenzer, T. Pelka, S. Möllenbeck and M. Horn-von Hoegen, Phys. Rev. B **77**, 125410 (2008)
 B. Krenzer, A. Hanisch-Blicharski, ..., R. Meyer, M. Horn-von Hoegen, Phys. Rev. B **80**, 024307 (2009)
 T. Witte, T. Frigge, B. Hafke, B. Krenzer, and M. Horn-von Hoegen, Appl. Phys. Lett. **110** (2017) 243103
 A. Hanisch-Blicharski et al., Nano Letters **21**, 7145 (2021)

Ultrafast fs-RHEED: 3rd generation

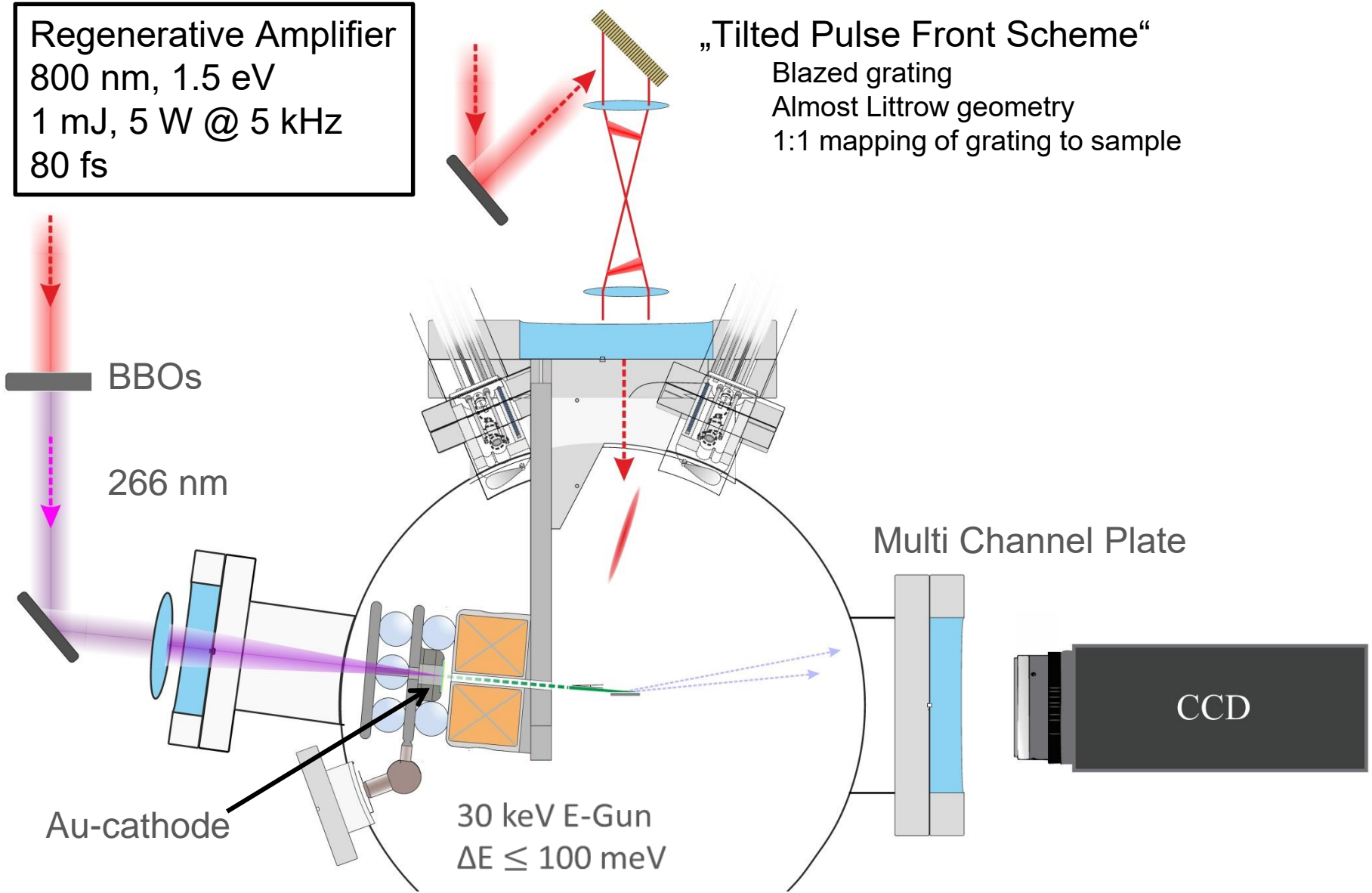


B. Hafke, T. Witte, C. Brand,
M. Horn-von Hoegen, Th. Duden,
Rev. Sci. Instr. **90**, 045119 (2019)

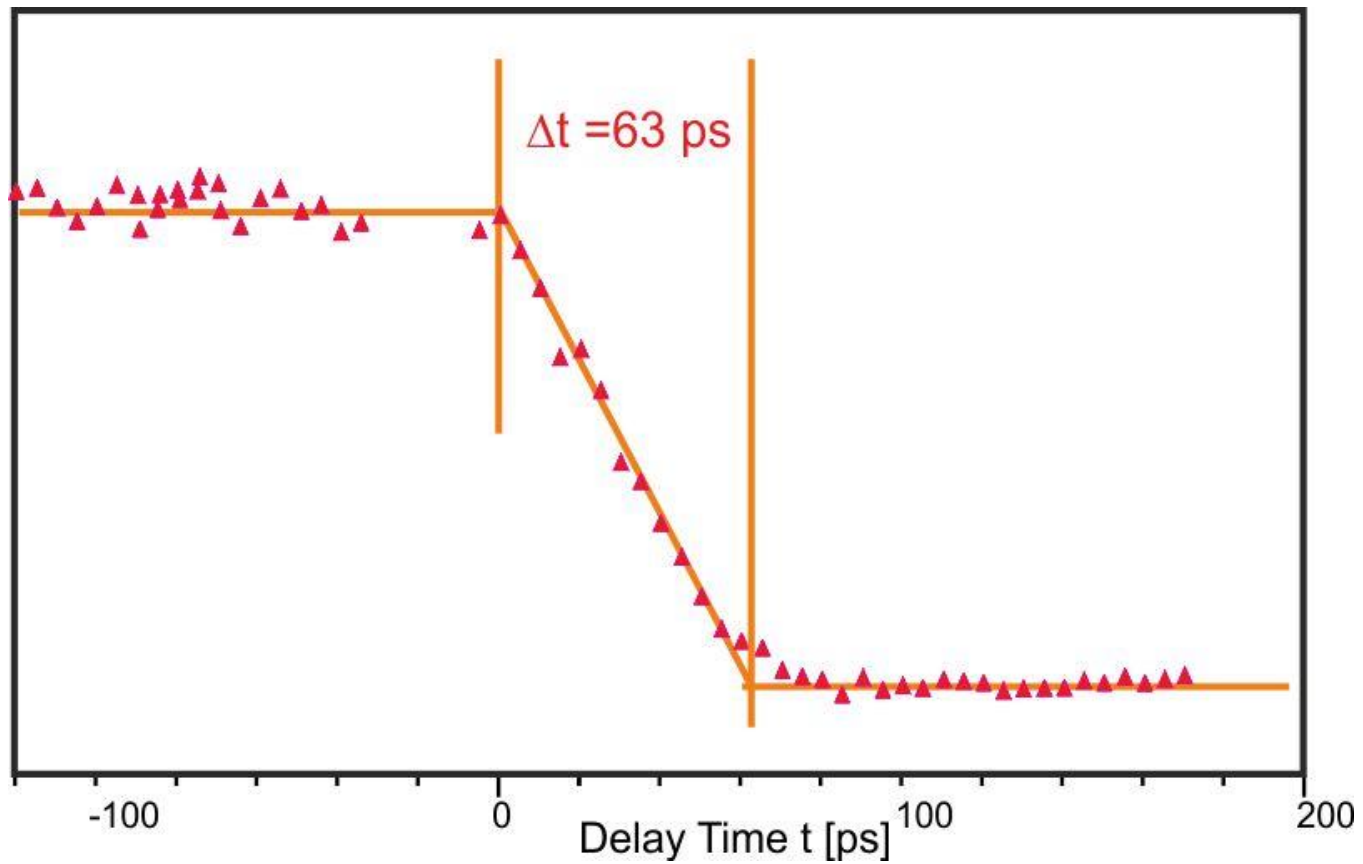
Ultrafast fs-RHEED: 3rd generation

Regenerative Amplifier
800 nm, 1.5 eV
1 mJ, 5 W @ 5 kHz
80 fs

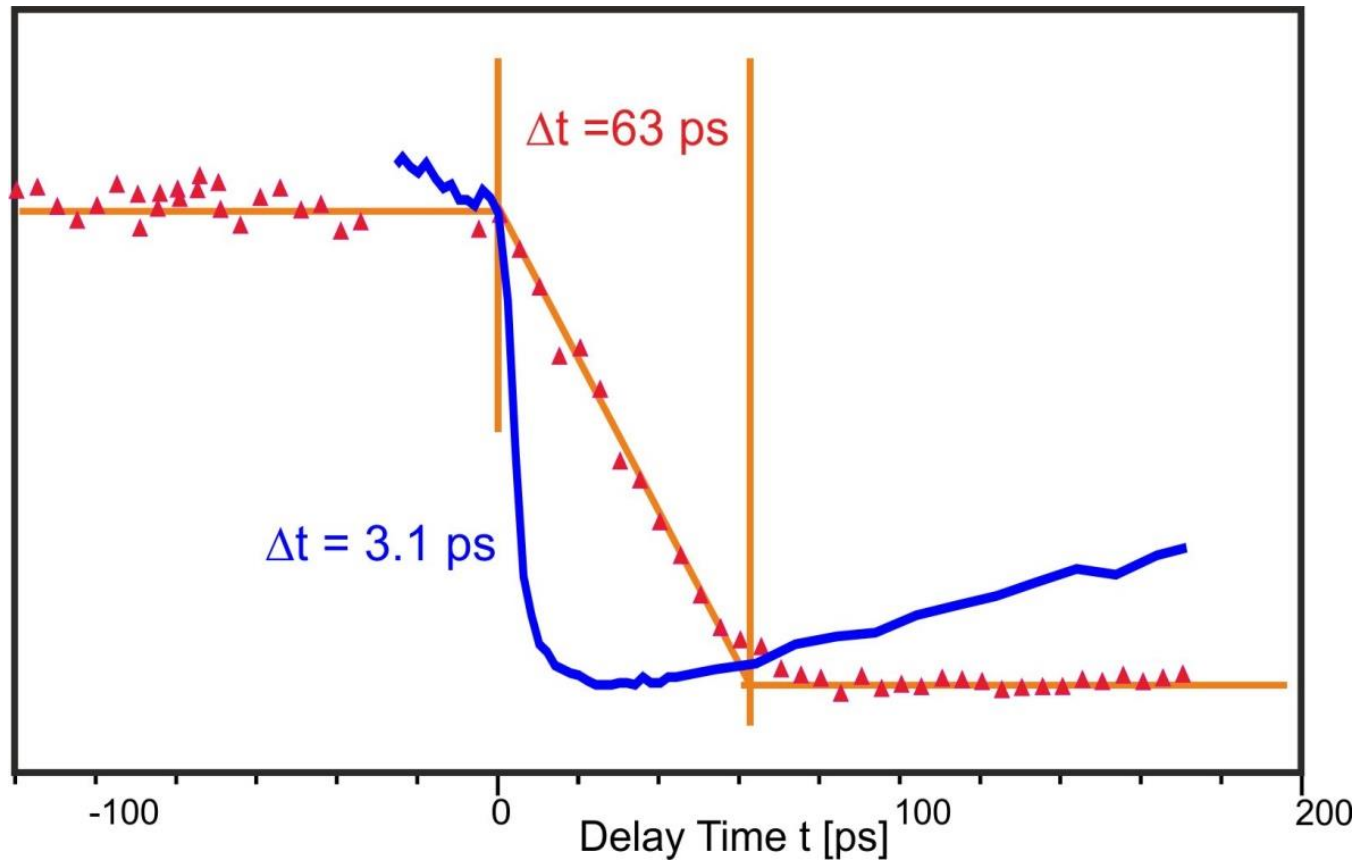
„Tilted Pulse Front Scheme“
Blazed grating
Almost Littrow geometry
1:1 mapping of grating to sample



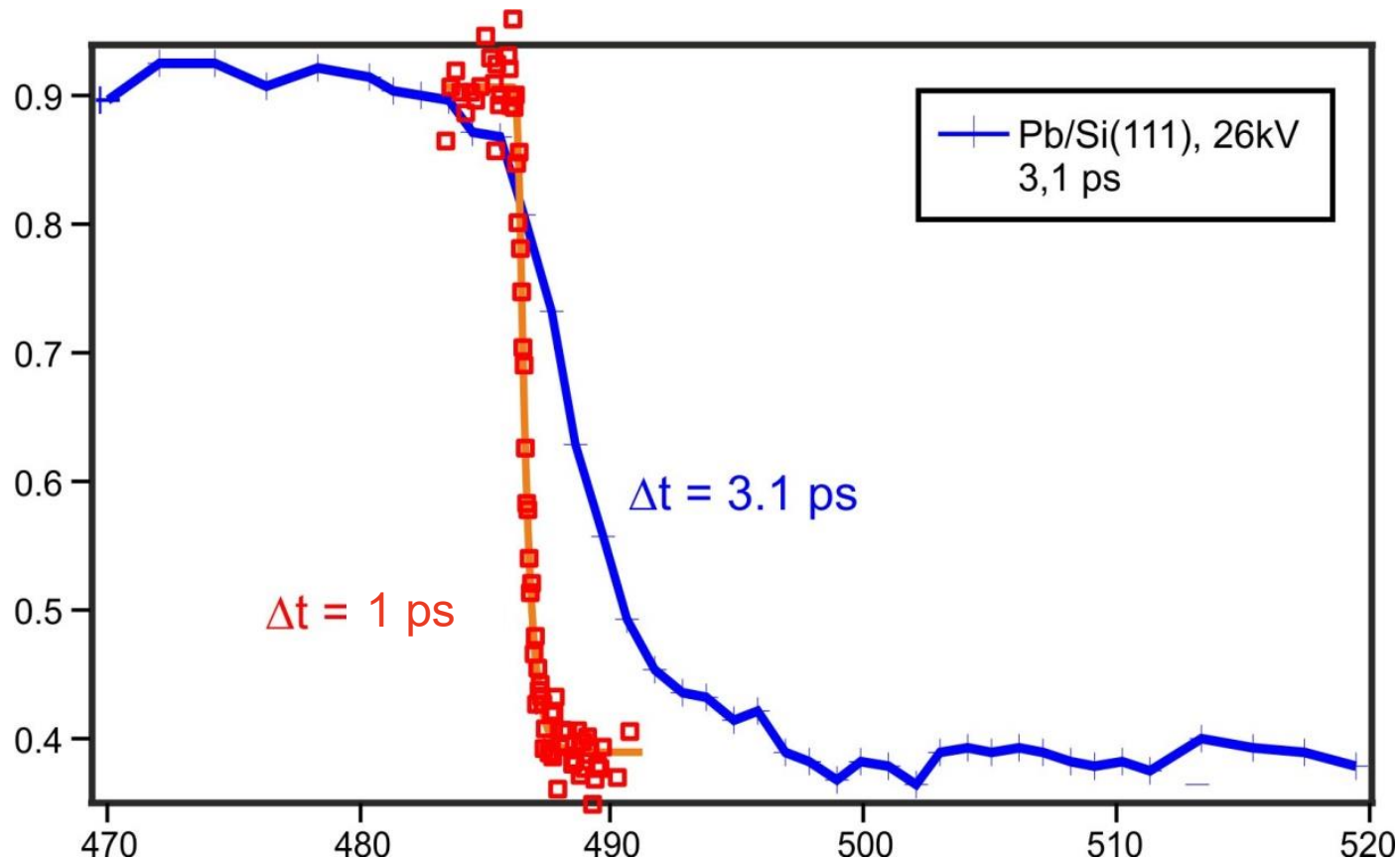
Heating of Bi(111) Film on Si(111) @ 80 K



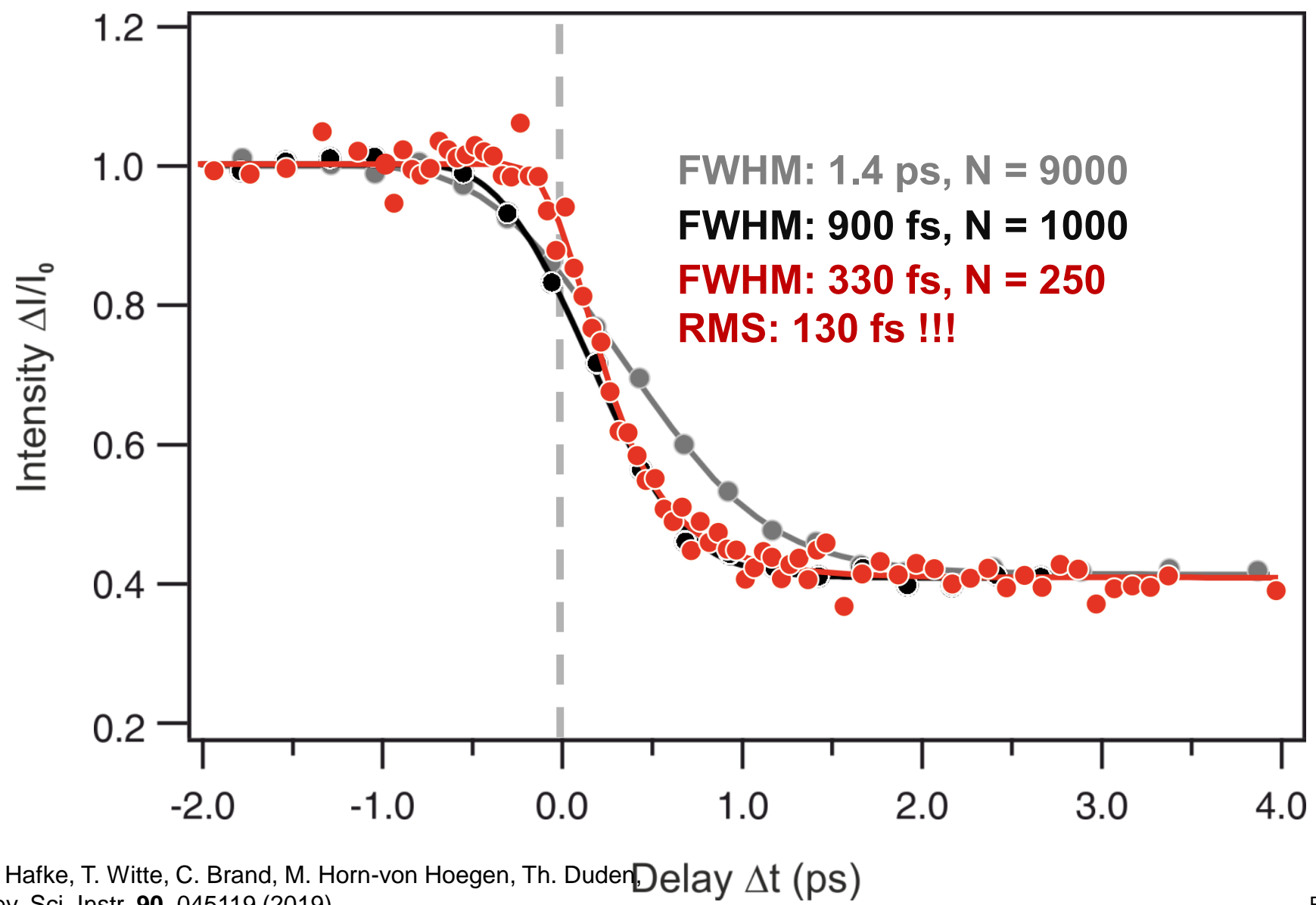
Pb islands on Si(111) @ 80 K ...



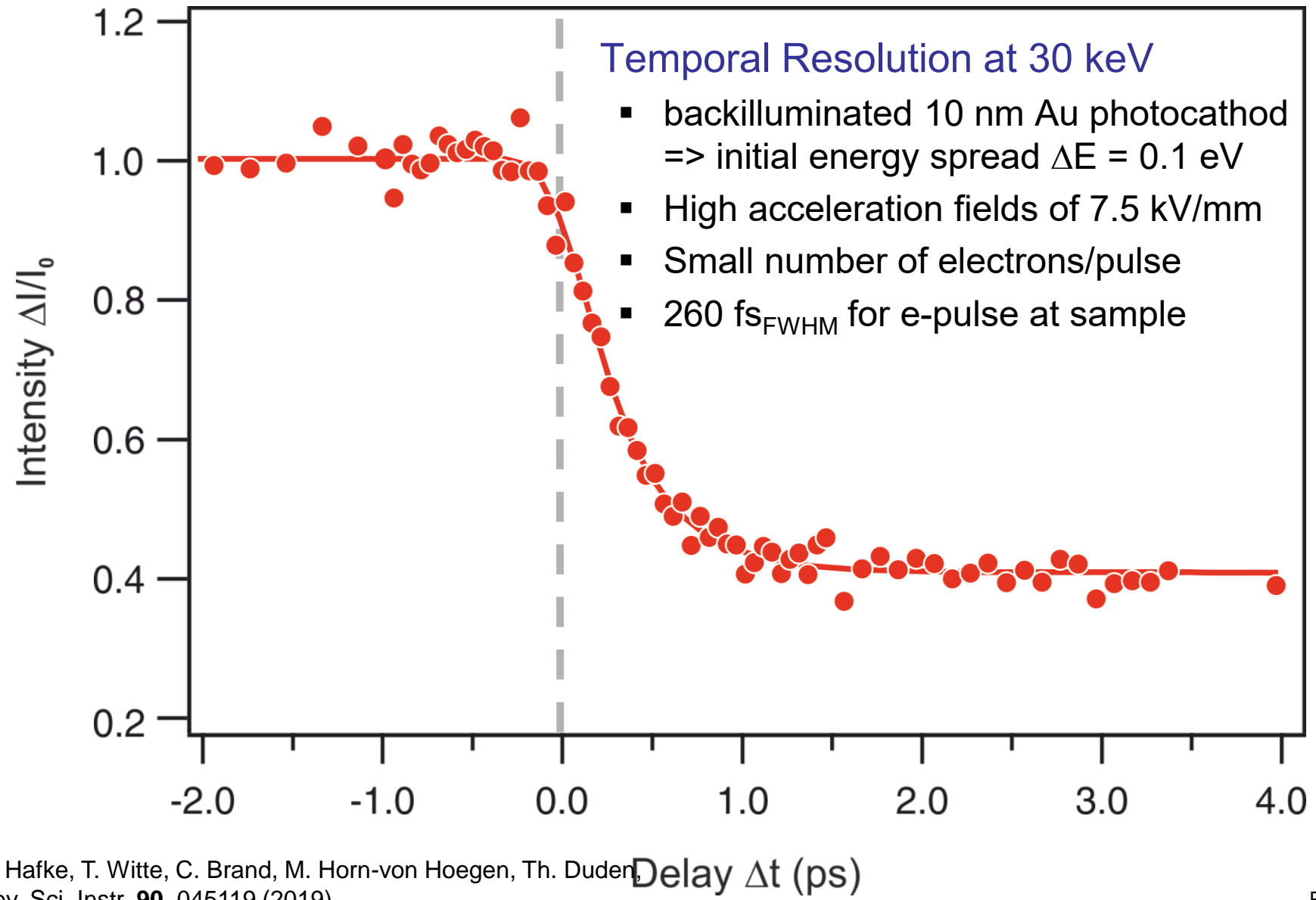
In on Si(111) @ 30 K ...



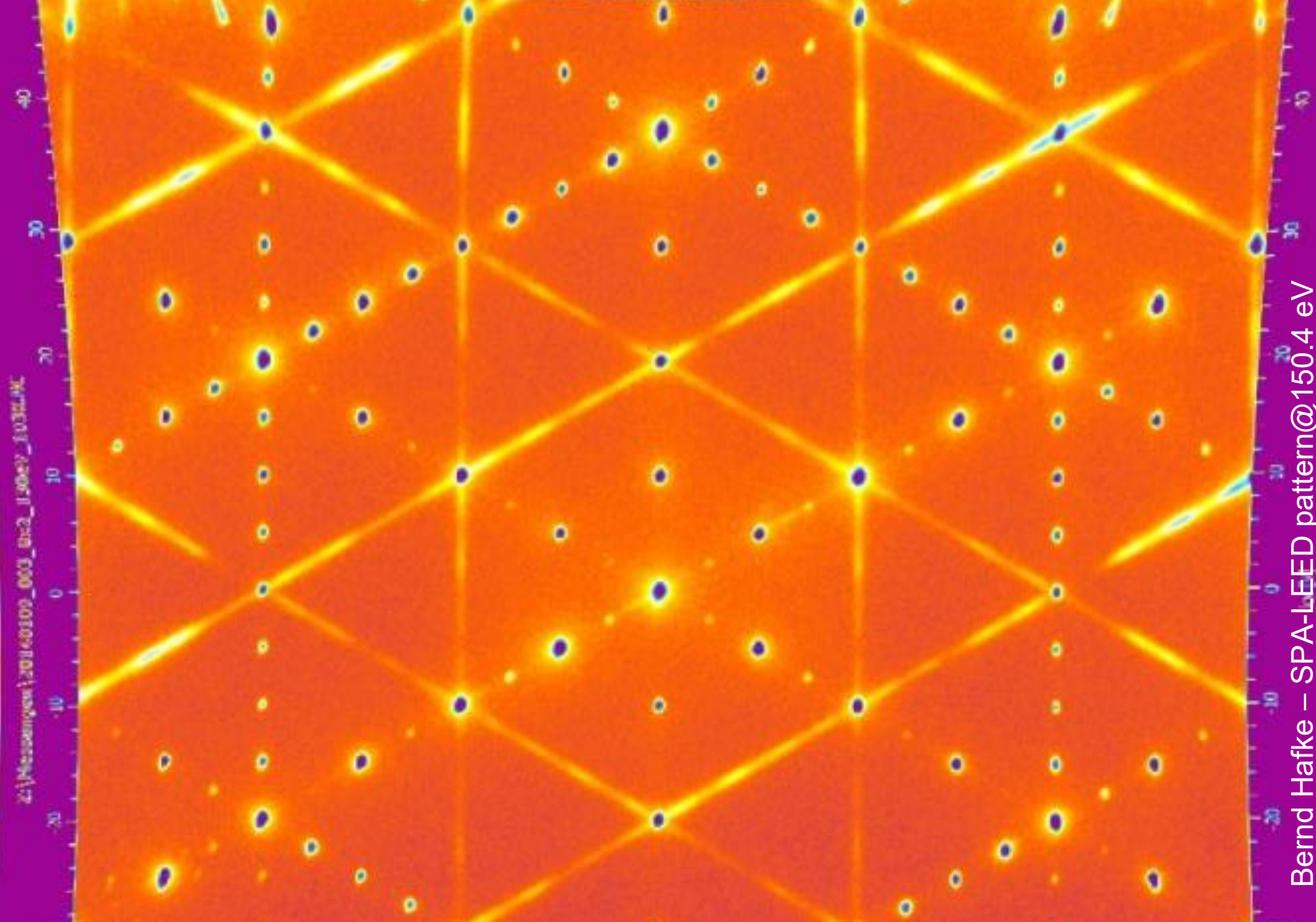
Ultimate Temporal Resolution !



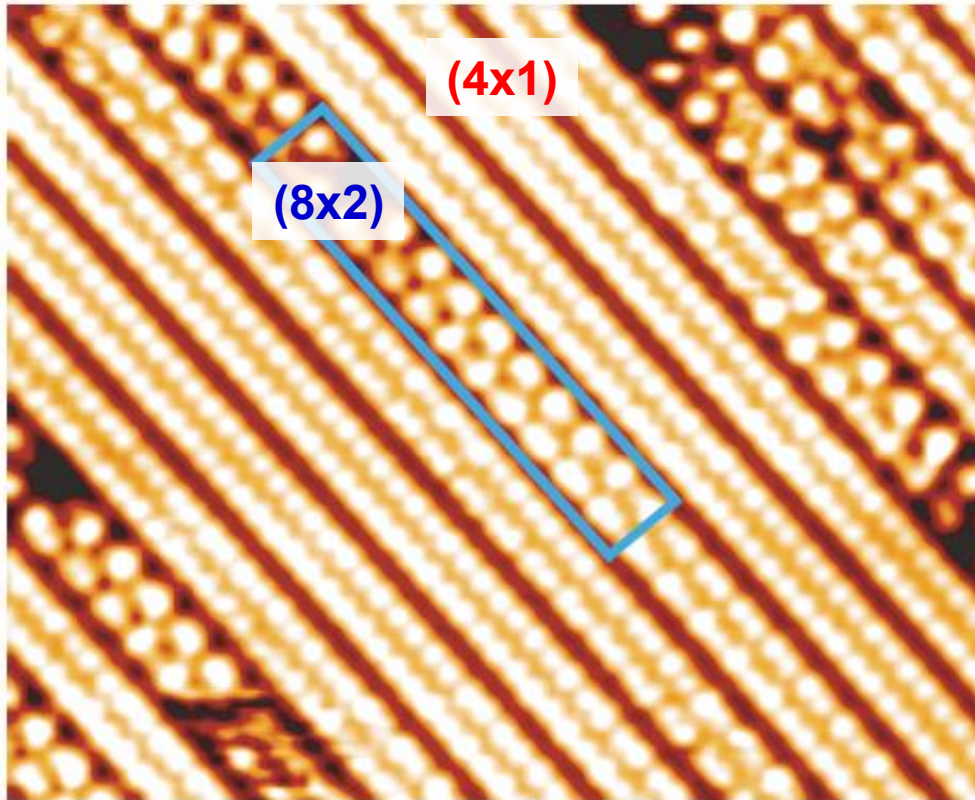
Ultimate Temporal Resolution



Si(111)-In(8x2) – ground state



Si(111)-In(8x2) ↔ (4x1)

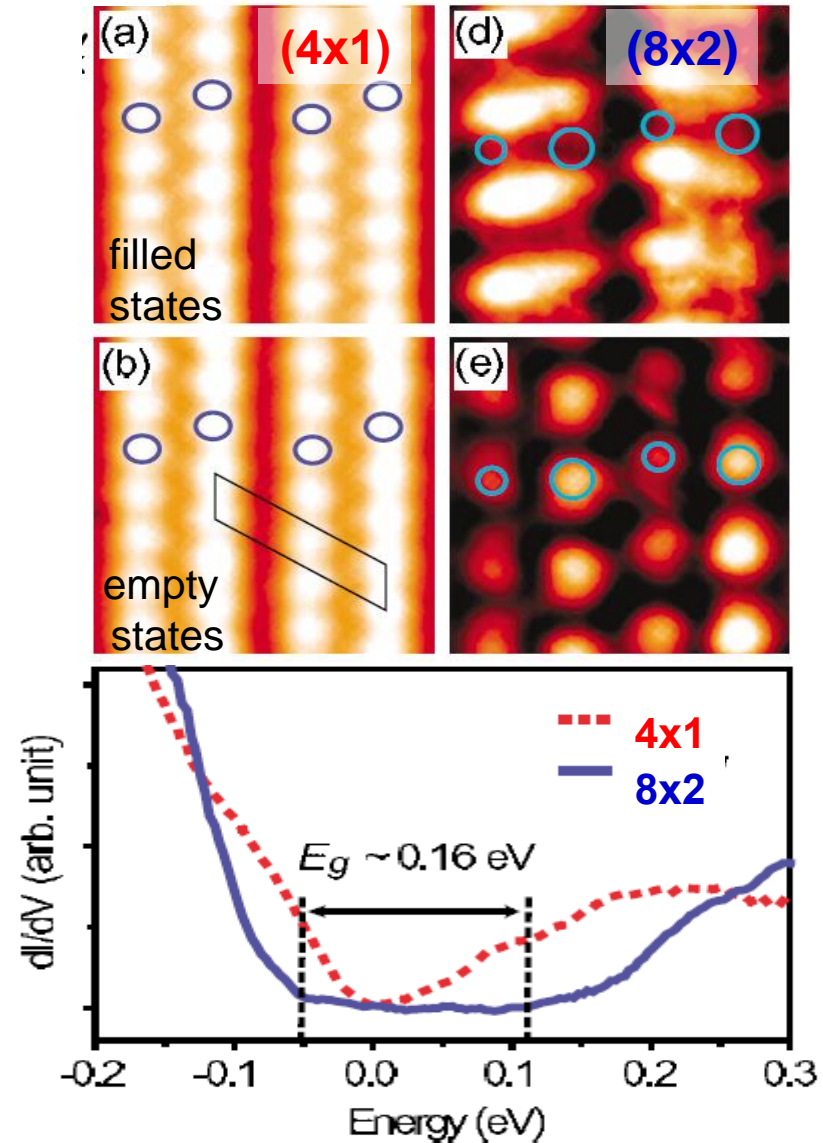


S. J. Park, H.W. Yeom, S. H. Min, D.H. Park, and I.-W. Lyo,
Phys. Rev. Lett. **93**, 106402 (2004)

Prototypical atomic wire system:

- metal-insulator transition
- opening of 0.16 eV bandgap
- symmetry breaking

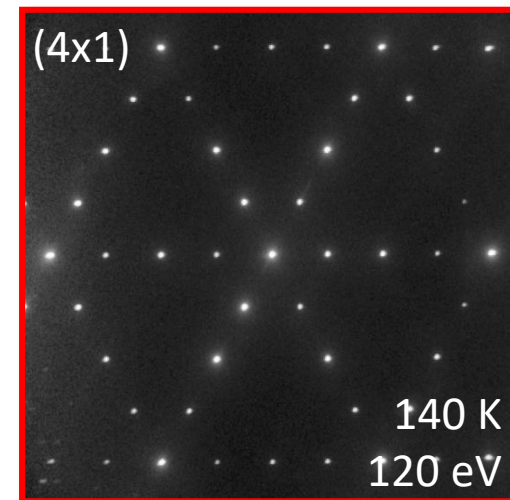
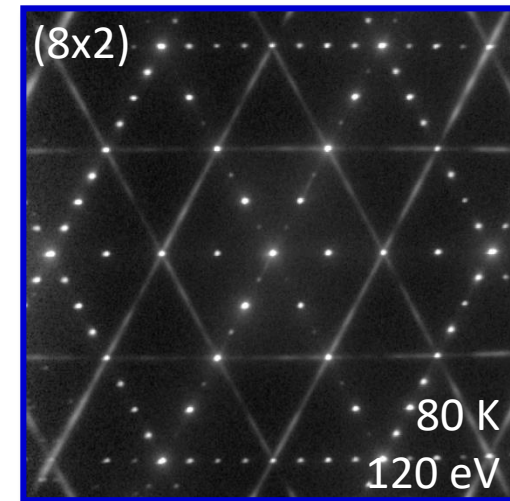
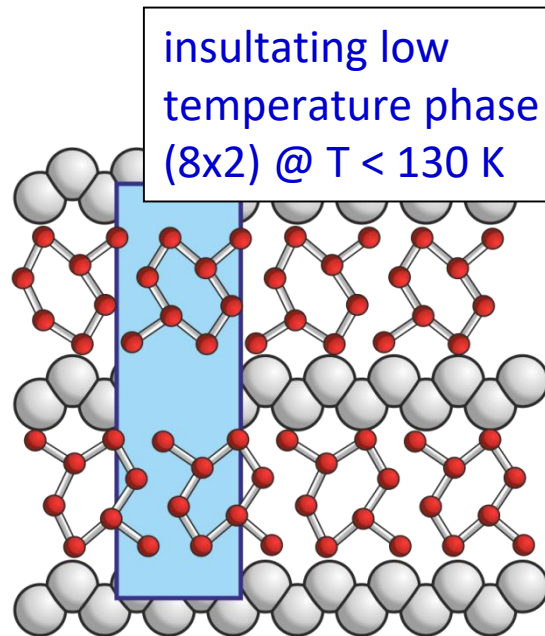
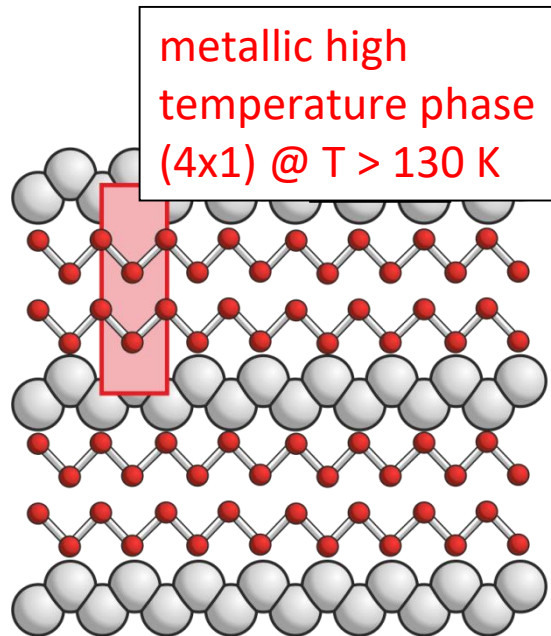
high temperature low temperature



Phase transition of In/Si(111)

In(4x1)/Si(111) – a quasi 1D atomic wire system

Below $T_c \sim 130$ K phase transition into (8x2):
insulating phase, periodicity doubling,
formation of charge density wave

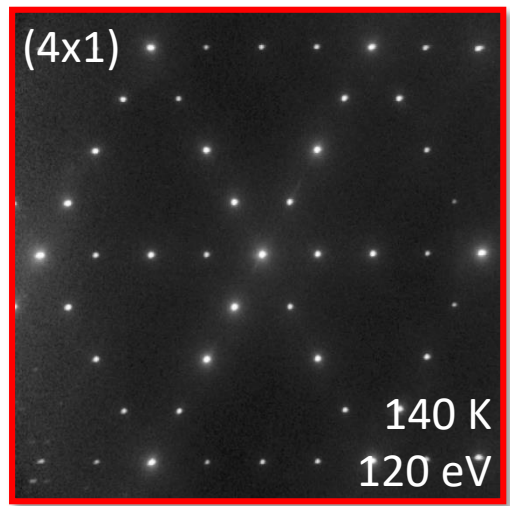
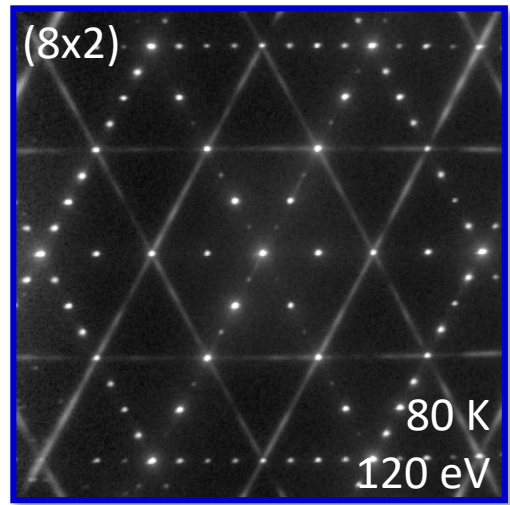
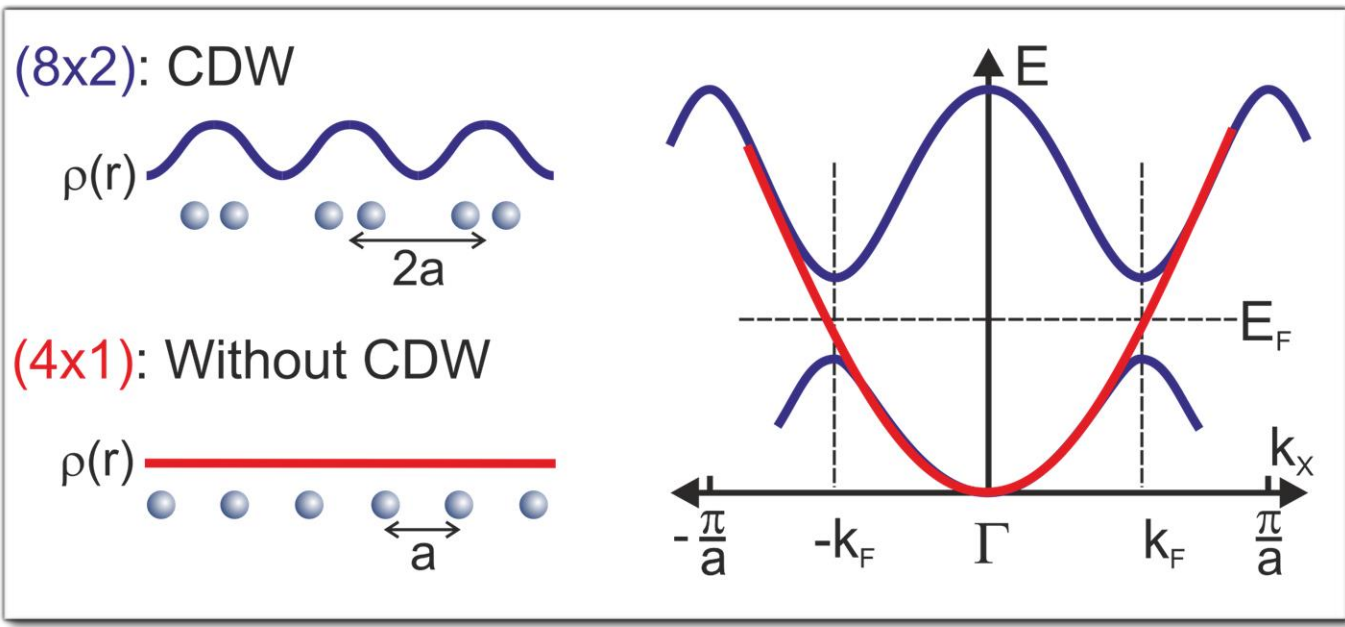


H. W. Yeom, S. Takeda, E. Rotenberg, I. Matsuda, K. Horikoshi,
J. Schaefer, C. M. Lee, S. D. Kevan, T. Ohta, T. Nagao,
S. Hasegawa, Phys. Rev. Lett. **82**, 4898 (1999),
S.V. Ryjkov, et al., Surf. Sci. **488**, 15 (2001).

G. Falkenberg, R.L. Johnson, R. Feidenhans'l et al.,
Phys. Rev. B **59** 12228 (1999)

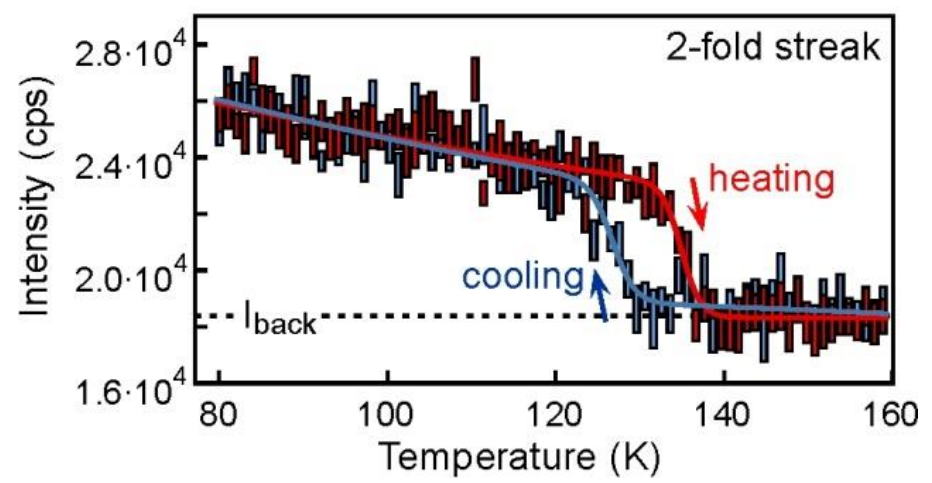
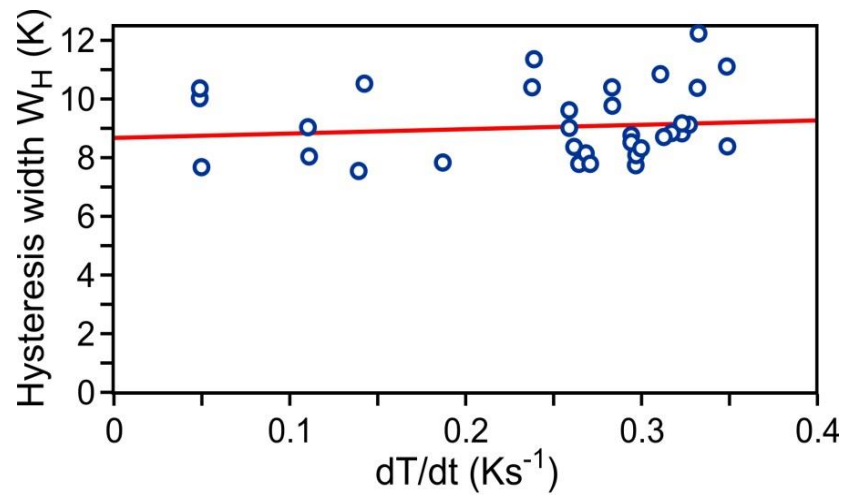
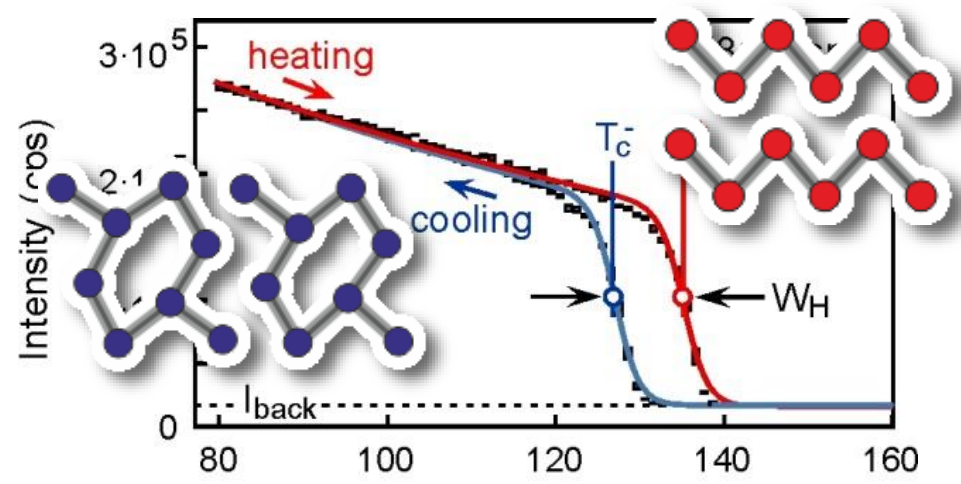
C. Kumpf, O. Bunk, J.H. Zeysing, Y. Su, M. Nielsen, R.L. Johnson,
R. Feidenhans'l, K. Bechgaard, Phys. Rev. Lett. **85**, 4916 (2000)

Peierls like structural instability



1st order transition

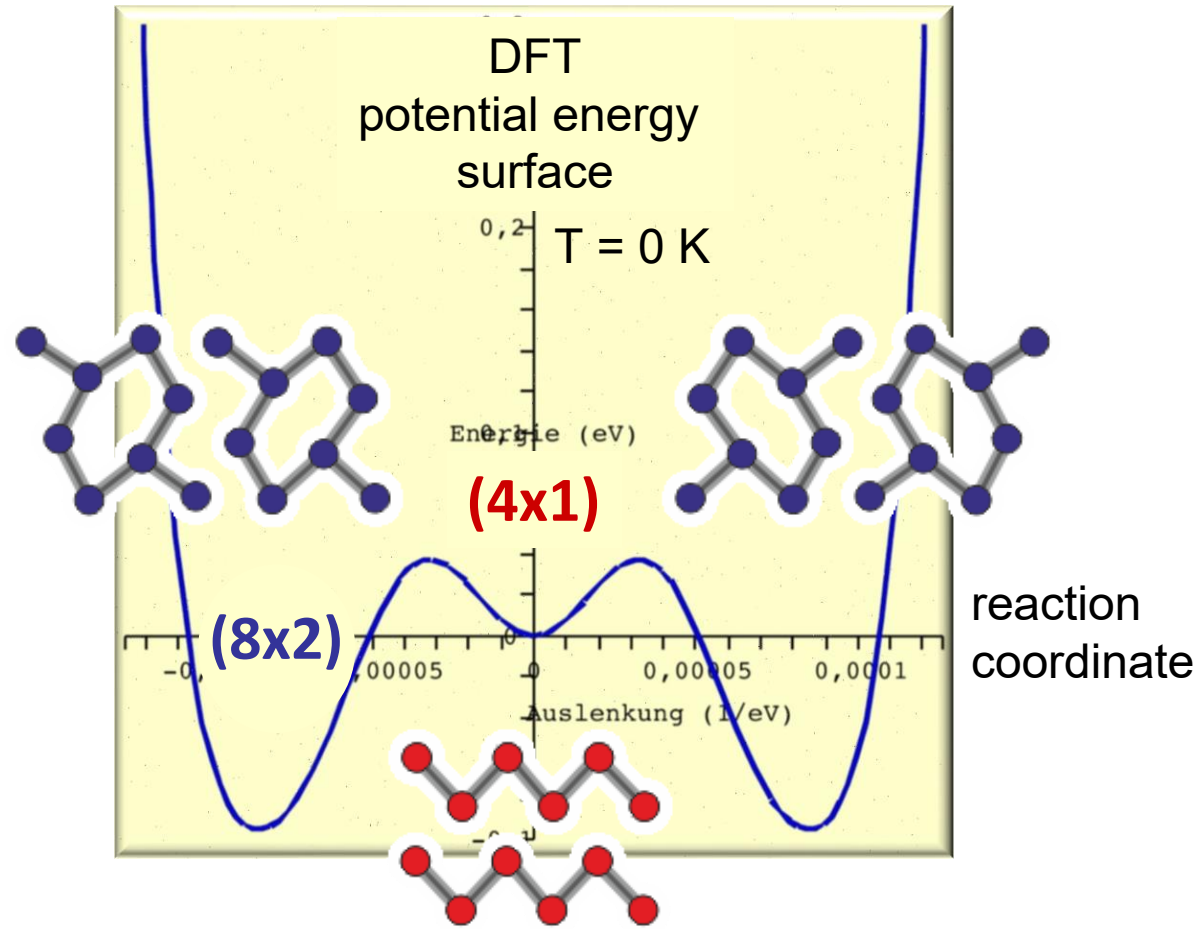
- Phase transition temperature $T_c = 130$ K
- Robust hysteresis of width $W_H = 10$ K
- Proof of **1st order** transition
=> Peierls like distortion [*]
=> **not** order-disorder transition



F. Klasing, T. Frigge, B. Hafke, S. Wall, B. Krenzer, A. Hanisch-Blicharski, and M. Horn-von Hoegen
Phys. Rev. B **89**, 121107(R) (2014)

[*] S. Wippermann, W.G. Schmidt, Phys. Rev. Lett. **105**, 126102 (2010);

Energy barrier between (8x2) ↔ (4x1)

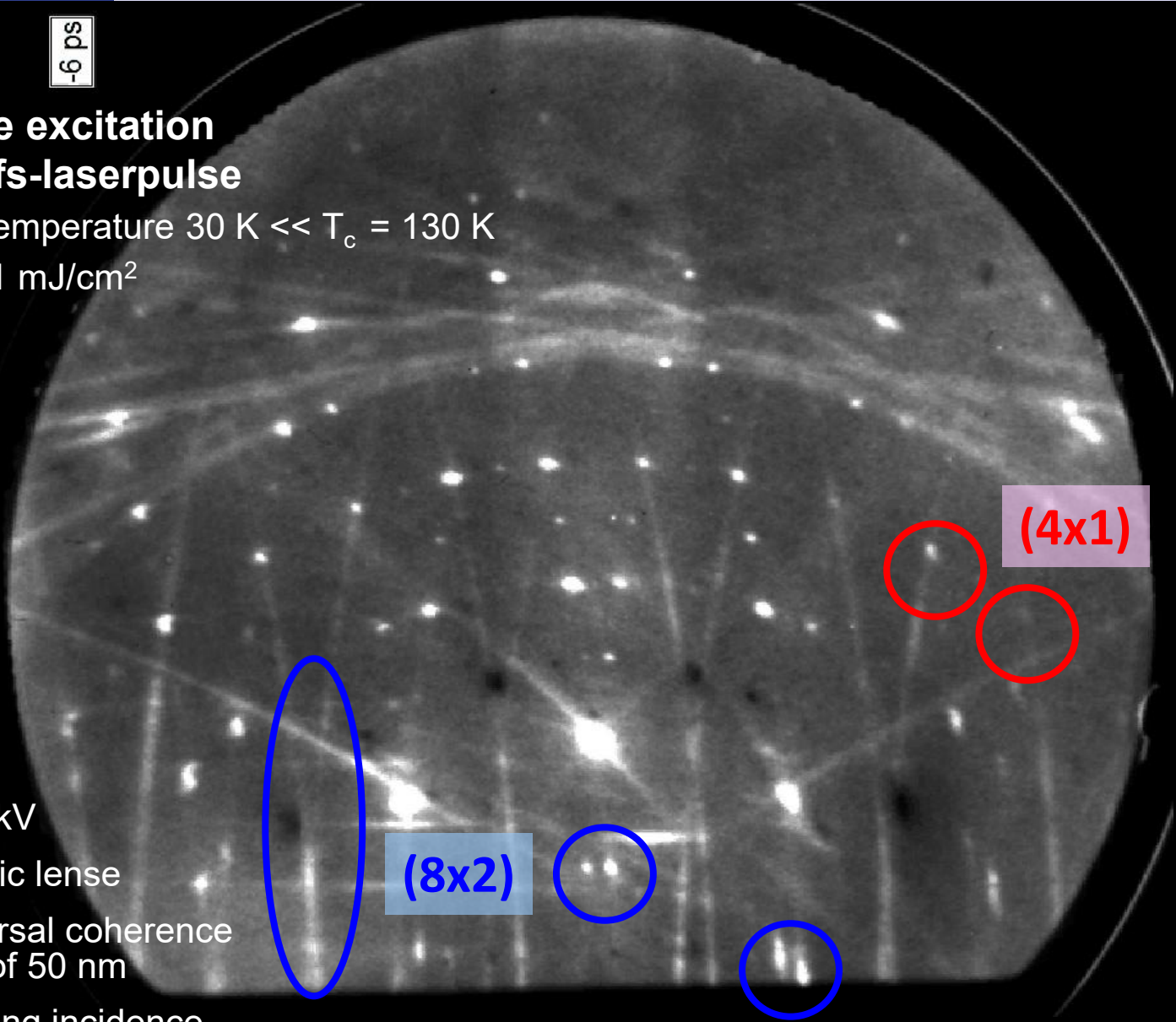


Movie of transition

-6 ps

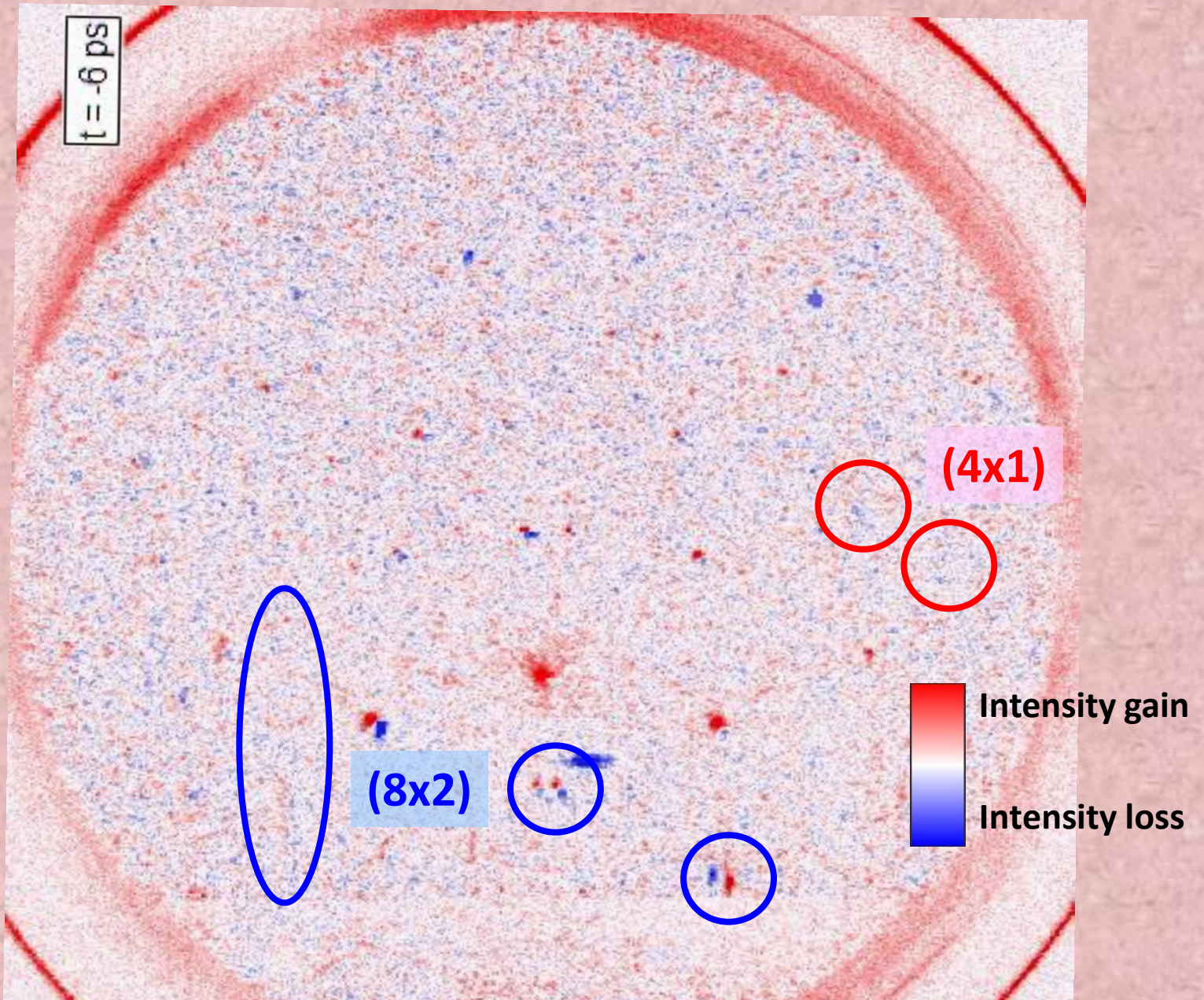
Impulsive excitation through fs-laserpulse

- Base temperature $30\text{ K} \ll T_c = 130\text{ K}$
- $\Phi = 2.1\text{ mJ/cm}^2$



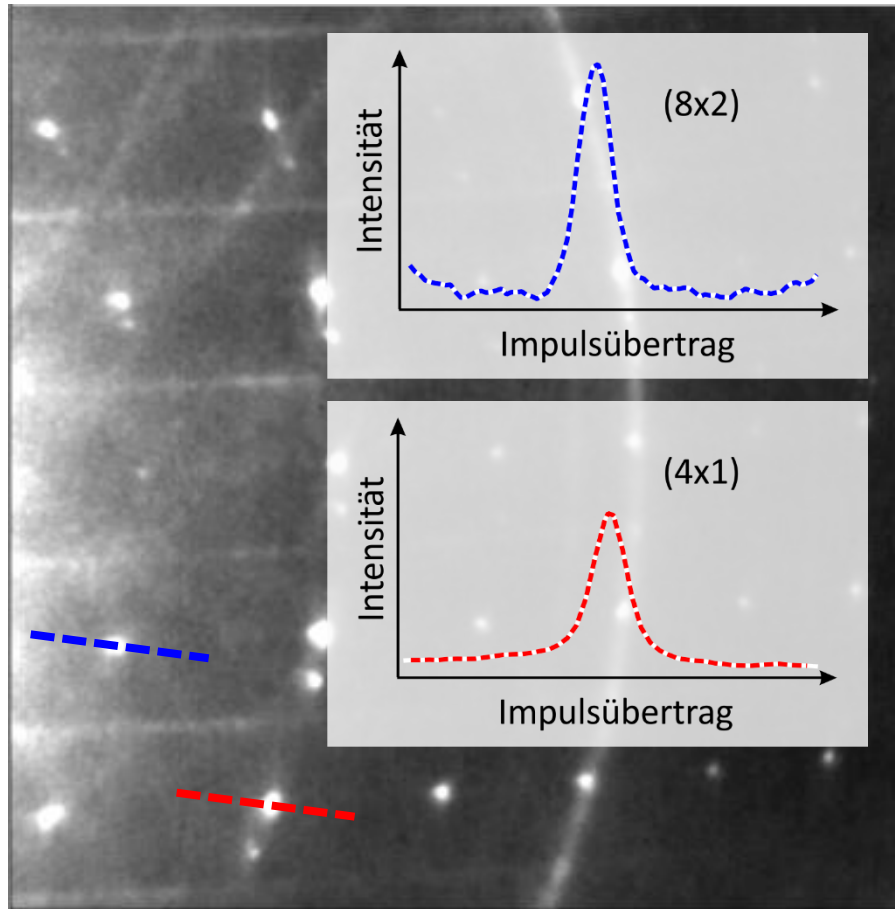
- $E = 30\text{ kV}$
- magnetic lens
- transversal coherence length of 50 nm
- 2° grazing incidence

Movie of transition – gains & losses

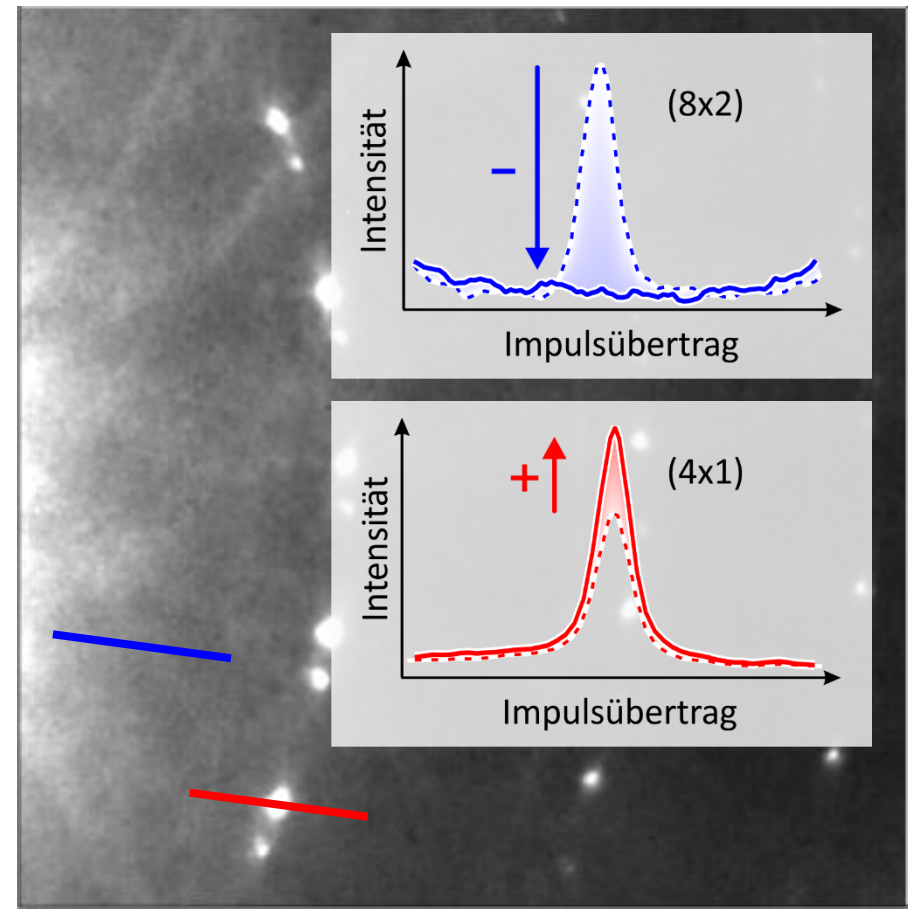


Lifting of ground state – how fast?

Si(111)(8x2)-In ground state,
prior to photo excitation $\Delta t < 0$ ps



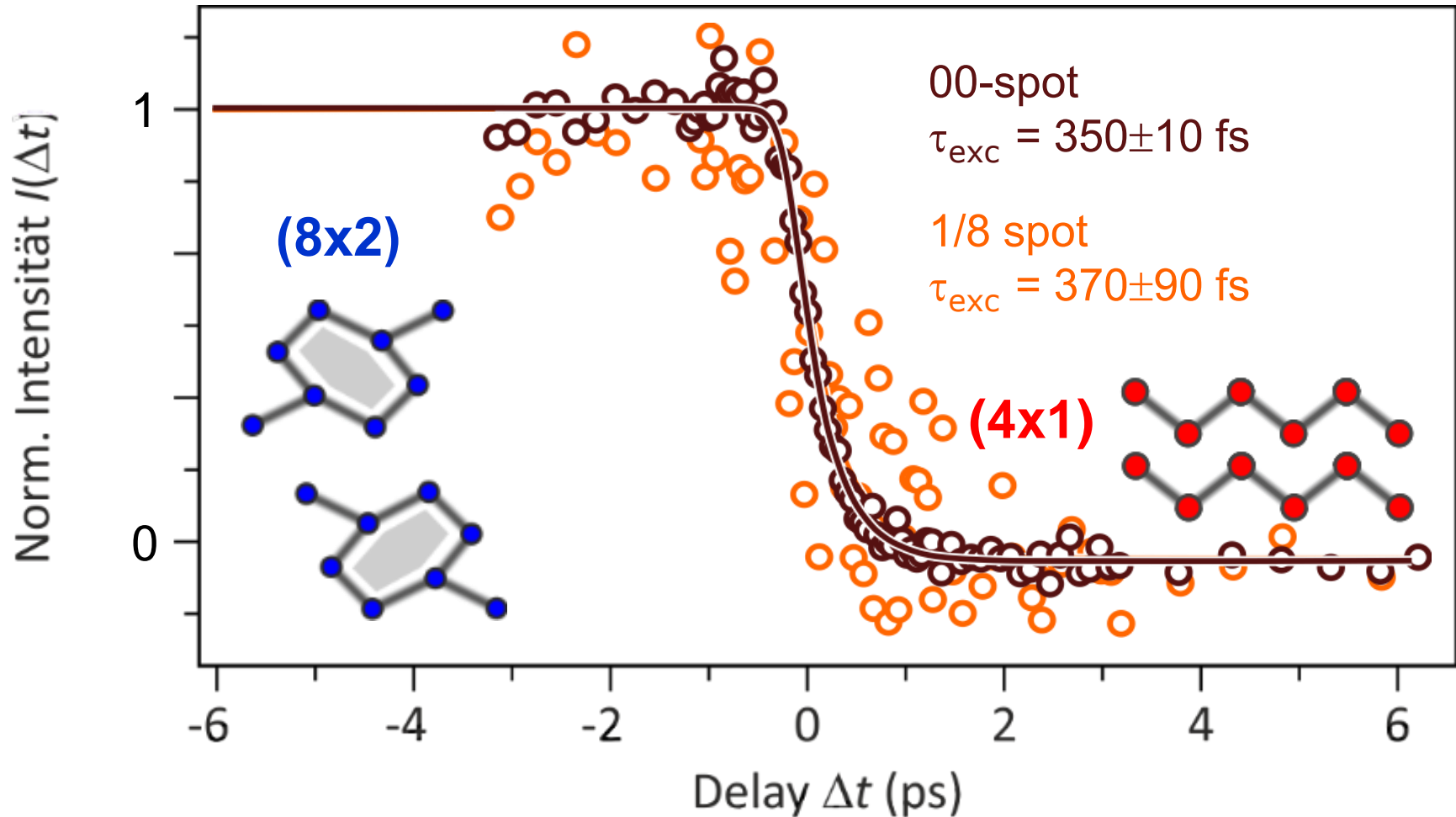
Si(111)(4x1)-In,
after photo excitation $\Delta t = 3$ ps



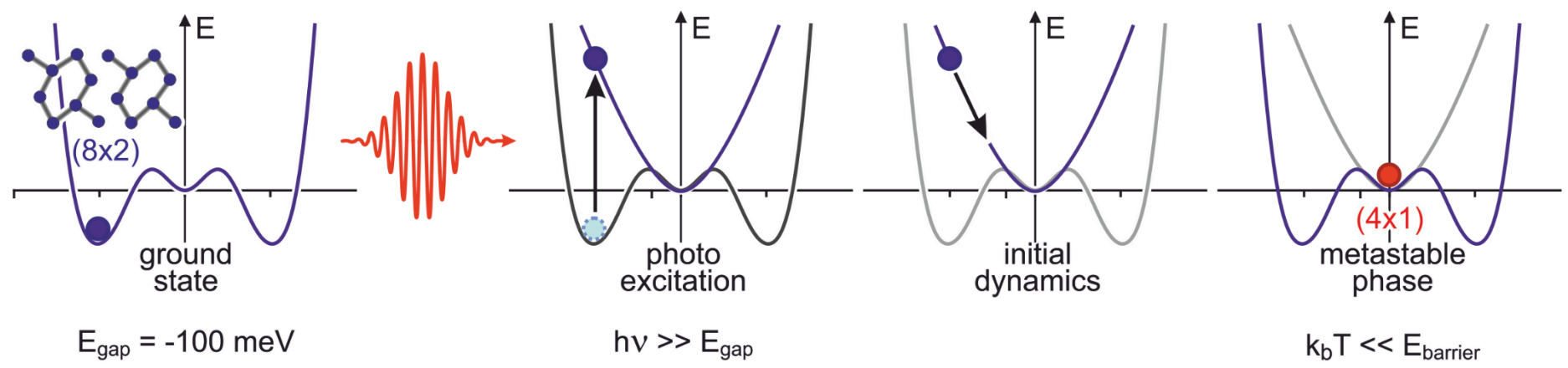
$T_0 = 30$ K, $\Phi = 6.7$ mJ/cm²

Lifting of low-T (8x2) ground state

$T_0 = 30$ K
 $\Phi = 6.7$ mJ/cm²

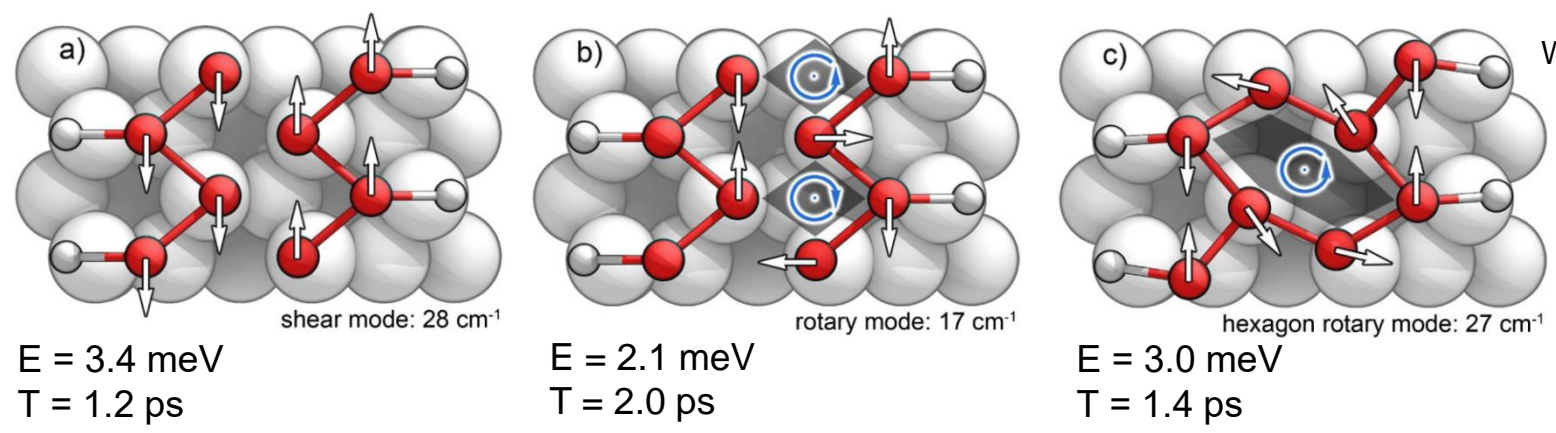


Accelerated displacive excitation



Transient changes of potential energy surface upon photo excitation:

- Accelerated displacive transition from (8x2) to (4x1) in 350 fs
- Transition in $\frac{1}{4}$ period of the characteristic shear and rotational soft phonon modes necessary for the structural change



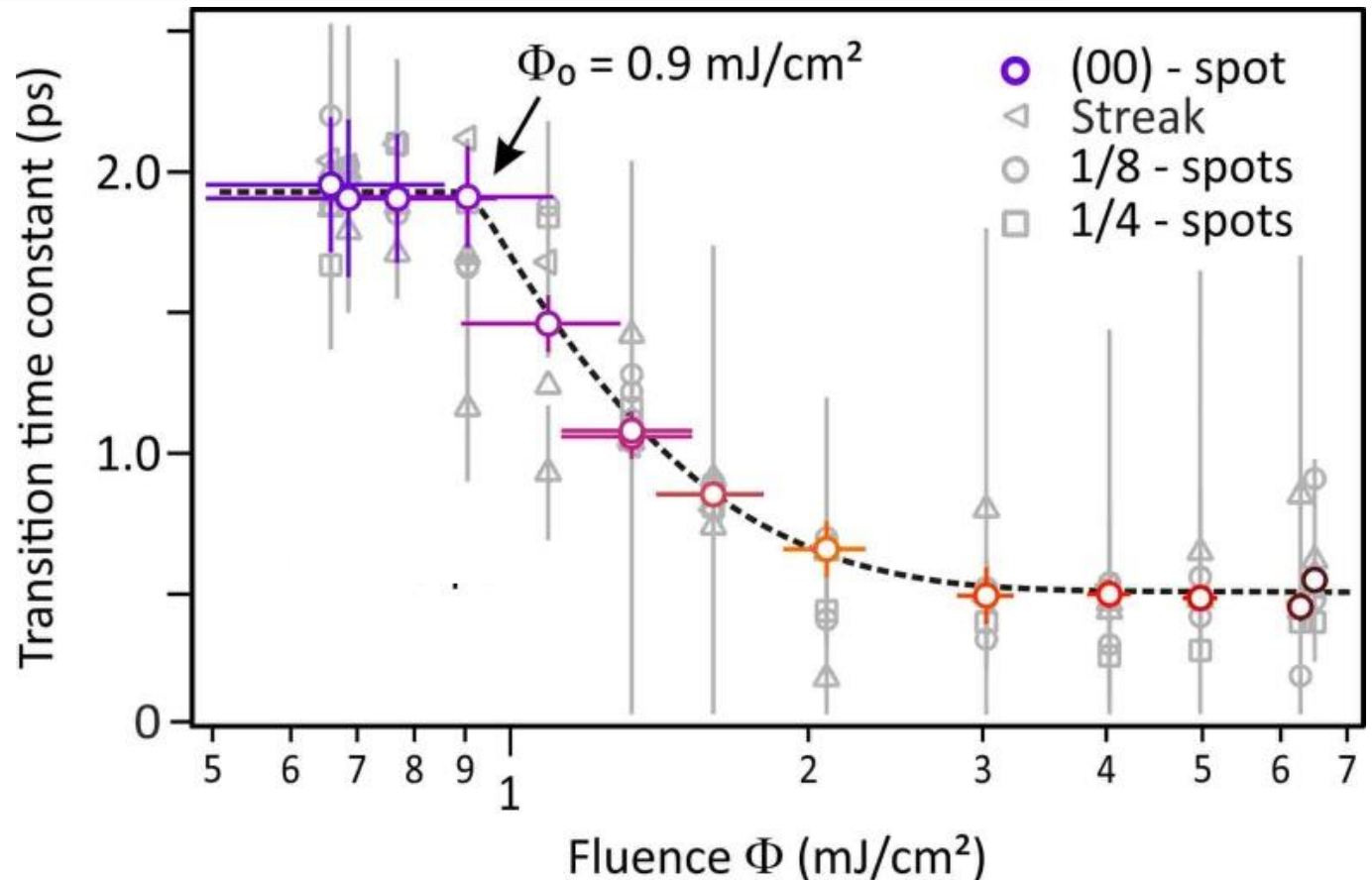
Wippermann et al.,
PRL **105**,
126102 (2010)

Fluence dependence of transition

Threshold fluence of 1 mJ/cm² for structural transition to (4x1)

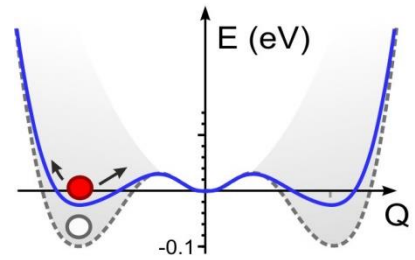
Increase of transition speed from 1 mJ/cm² up to 3 mJ/cm²

Saturation at $\tau = 350$ fs for the structural transition, i.e., motion of atoms, thus **fastest switching from insulator to metal!**



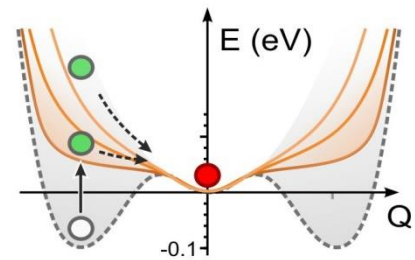
Accelerated displacive excitation

$\Phi < 1 \text{ mJ/cm}^2$



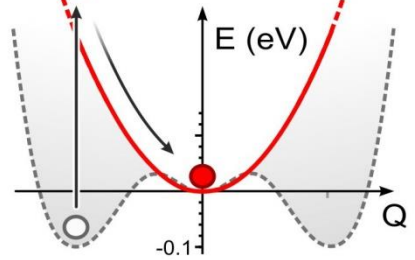
$\tau = 1900 \text{ fs}$

$\Phi \approx 1 - 2 \text{ mJ/cm}^2$



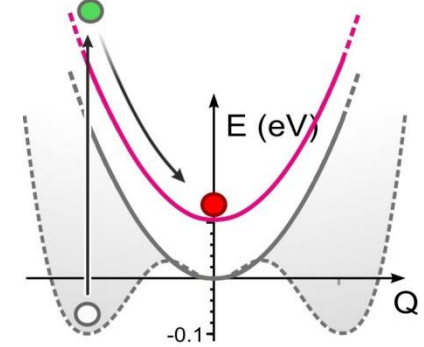
$\tau = 1900 - 350 \text{ fs}$

$\Phi \approx 2 - 3 \text{ mJ/cm}^2$

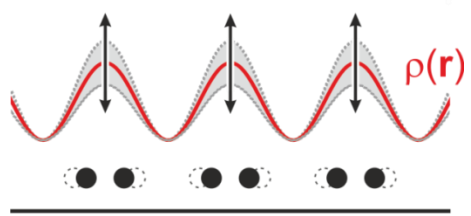


$\tau = 350 \text{ fs}$

$\Phi > 3 \text{ mJ/cm}^2$



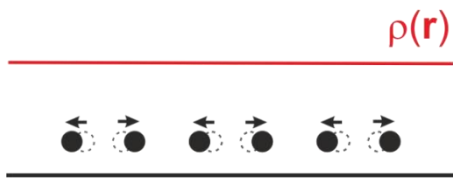
$\tau = 350 \text{ fs}$



Bandgap still open

Observation of collective CDW amplitudon mode !

J.G.Horstmann et al., Nature **583**, 232 (2020)



Bandgap closes

Incomplete melting of CDW:

Phase transition speeds up

Complete melting of CDW and strongly accelerated displacive transition:

Highest slope of free energy

Vertical shift of free energy curve:

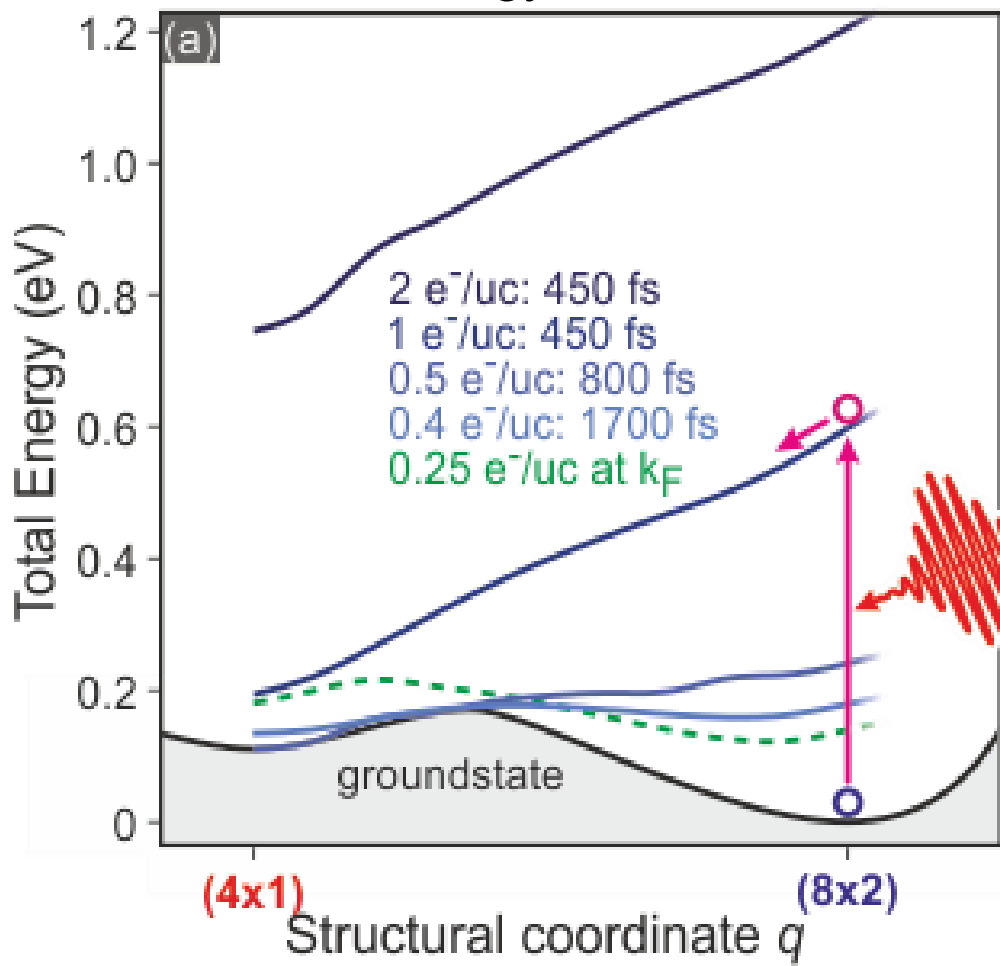
Saturation of acceleration

As fast as possible! => Quantum Limit

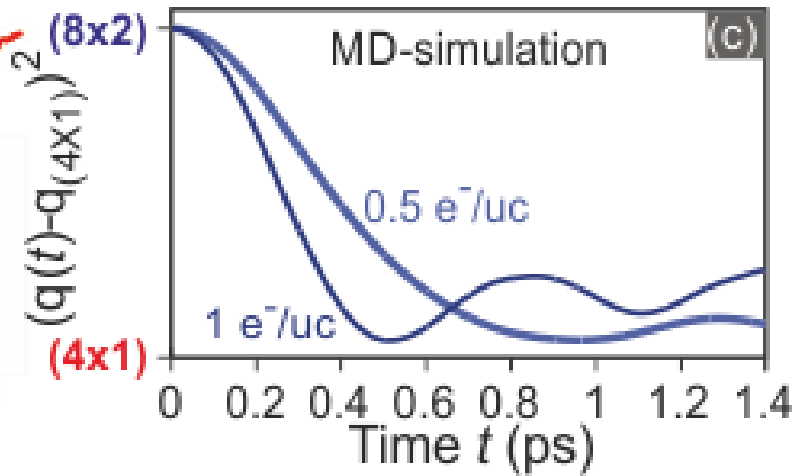
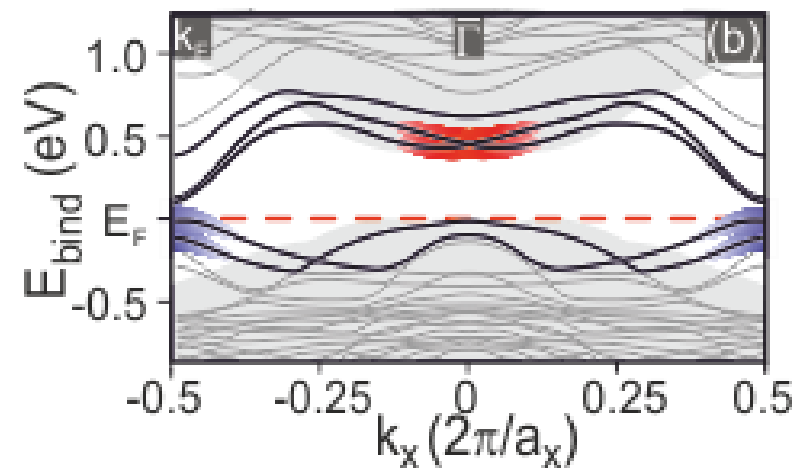
Quantum limit is the nonstatistical regime of rates in which the nuclear motion is directed and deterministic on the shortest scales of length (0.1–1 nm) and time (10^{-13} to 10^{-12} s)

C.Y. Ruan, F. Vigliotti, V.A. Lobastov, S. Chen, & A.H. Zewail, PNAS **101**, 1123 (2004)

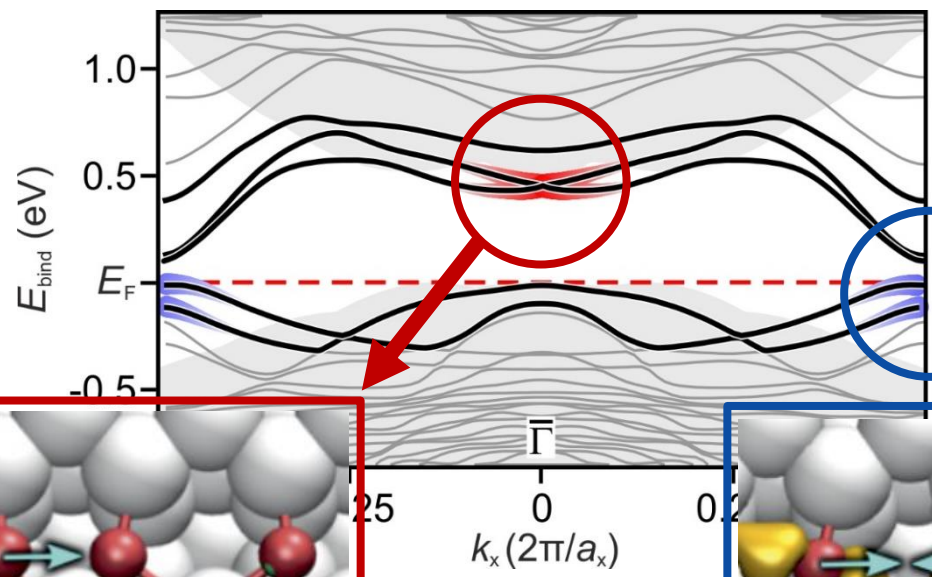
Potential Energy Surface



Band Structure

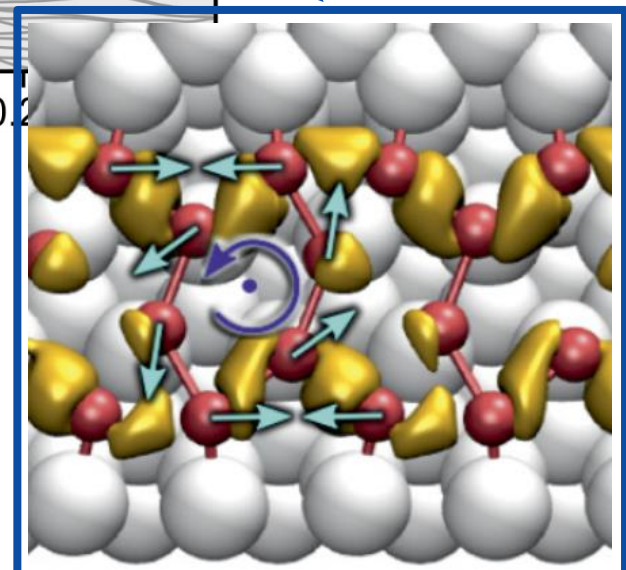
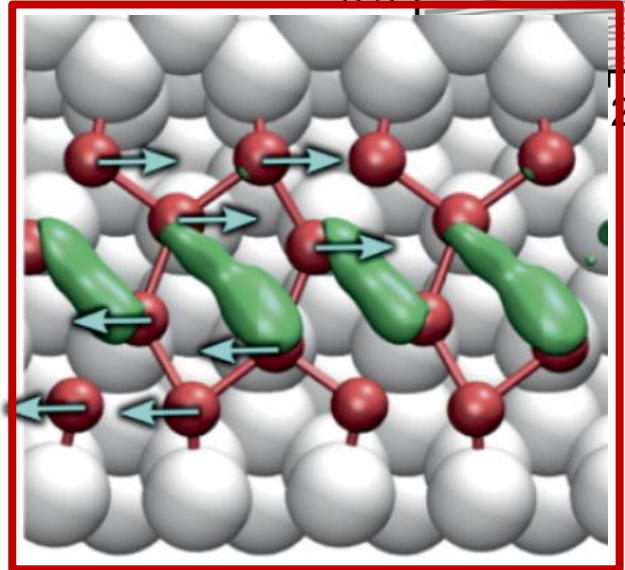


Specific electronic states drive PT



Pull !

Push !

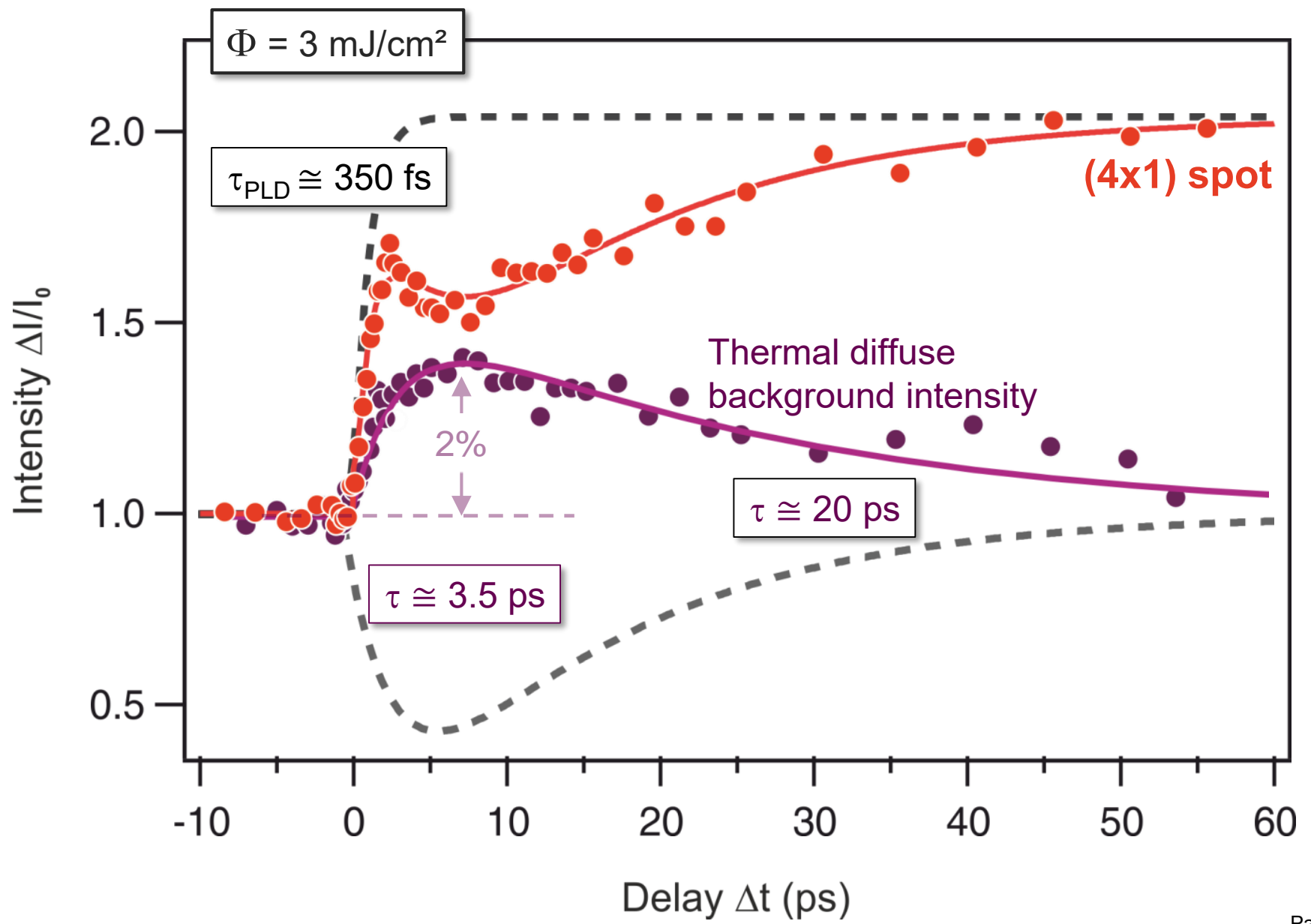


Electrons in conduction band at Γ
Population of bonding state
Excitation of soft shear mode

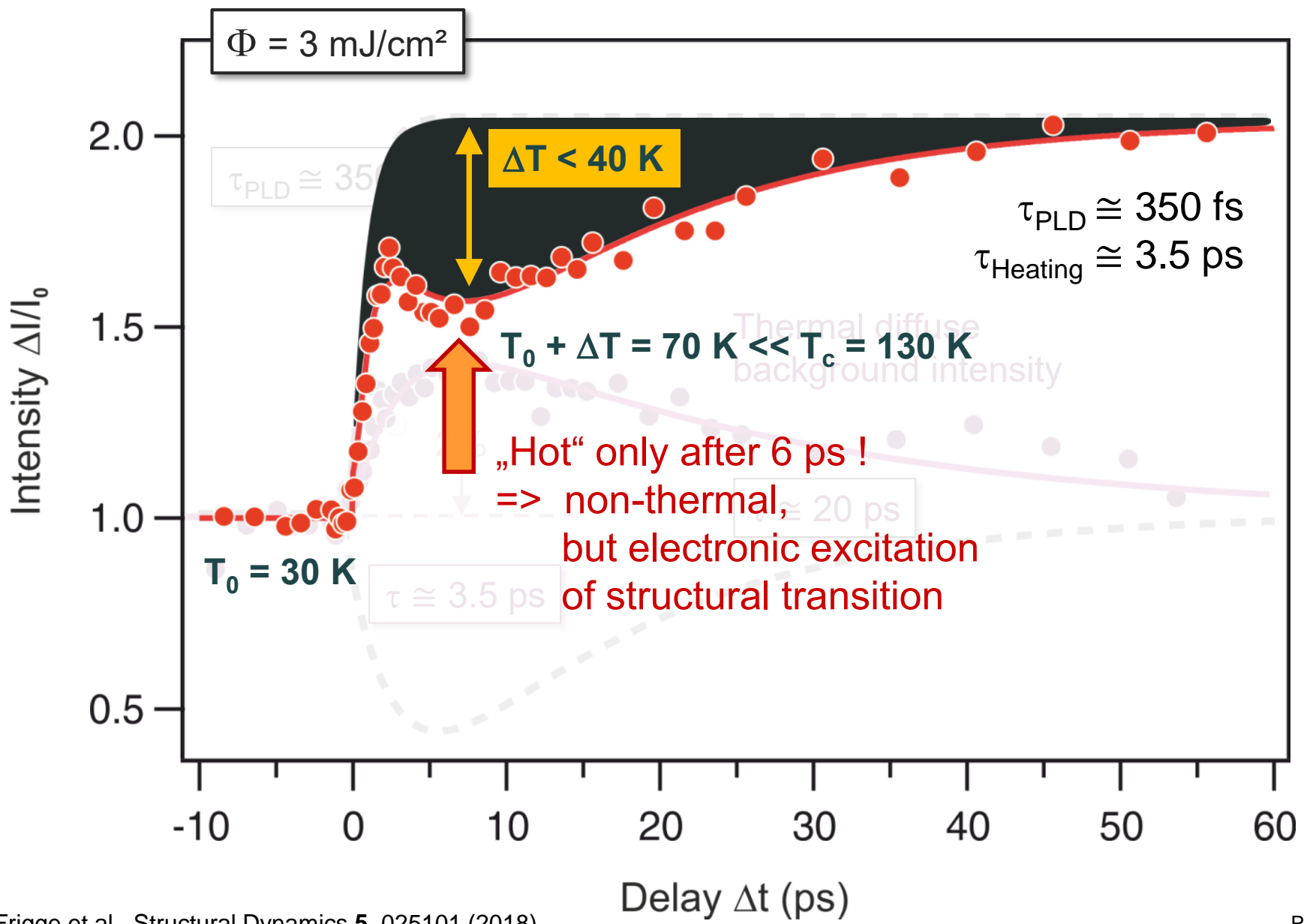
Holes in valence band at zone boundary
De-population of bonding states
Excitation of soft rotational mode

“Beyond the molecular movie: ultrafast dynamics of bands and bonds during a photo-induced phase transition”,
C.W. Nicholson et al., Science **362**, 821 (2018)

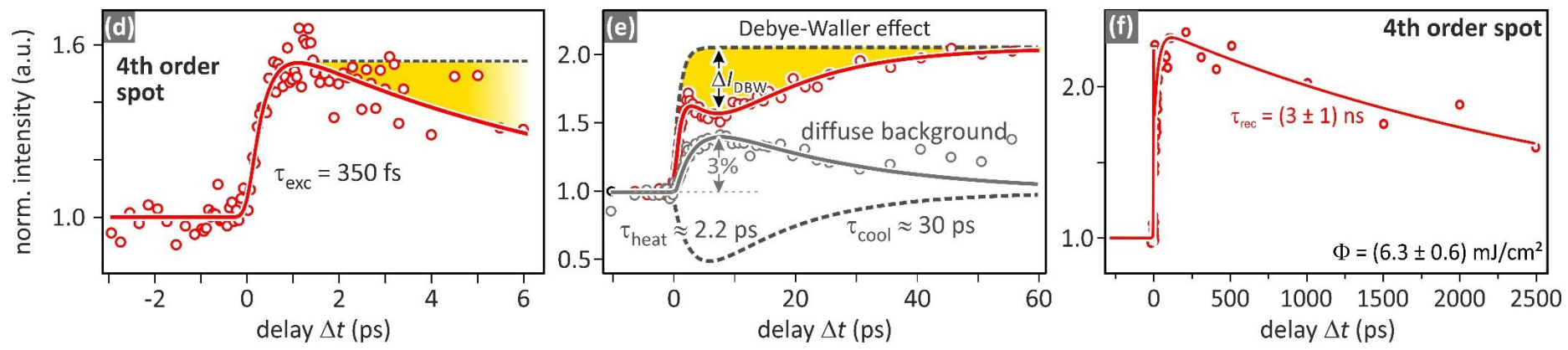
Thermal or non-thermal excitation?



Delayed thermal excitation

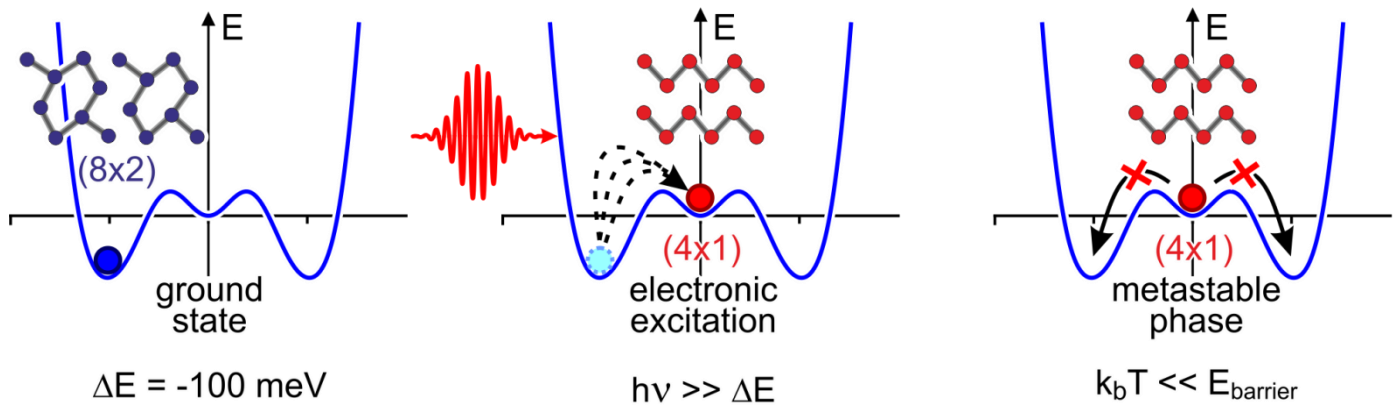


Slow recovery to groundstate

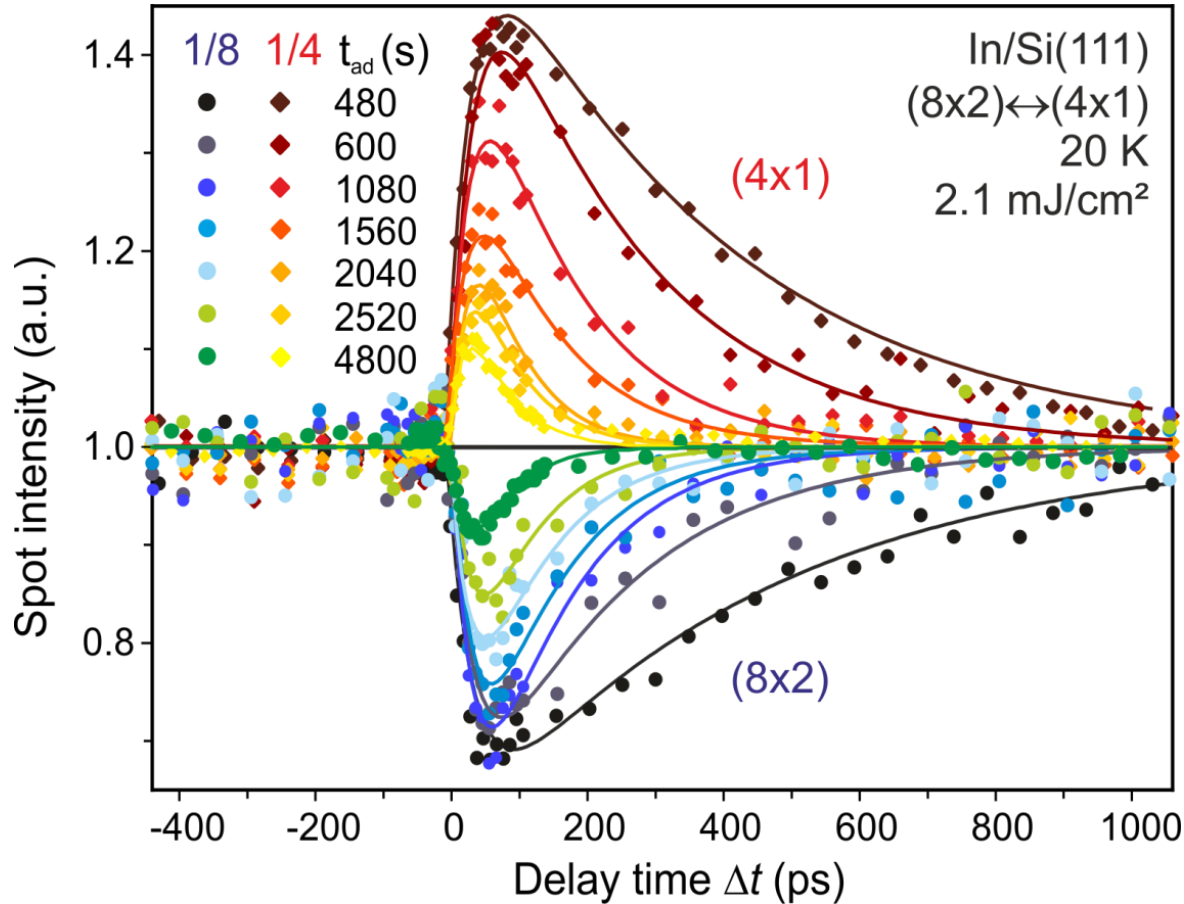


Supercooled metastable surface phase:

- 40 meV barrier hinders immediate recovery of (8x2) groundstate
- System is trapped in high temperature state - inaccessible under equilibrium



Adsorbates acting as seeds

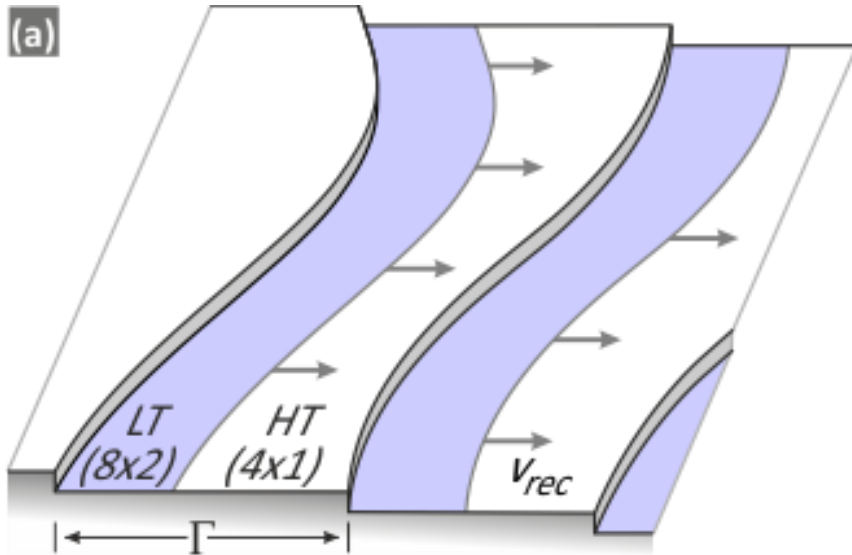


Recovery of groundstate sensitive to

- Adsorption from residual gas in UHV, most likely H₂O
- 1D-recovery front at 100 m/s

Extreme slow recovery of ground state

- Improved vacuum conditions - adsorbates acting as seed are not present
- Step edges trigger recovery of (8x2) ground state
- Use step morphology => determine velocity of 1-dim. recovery front through $v_{8x2} = s / t$

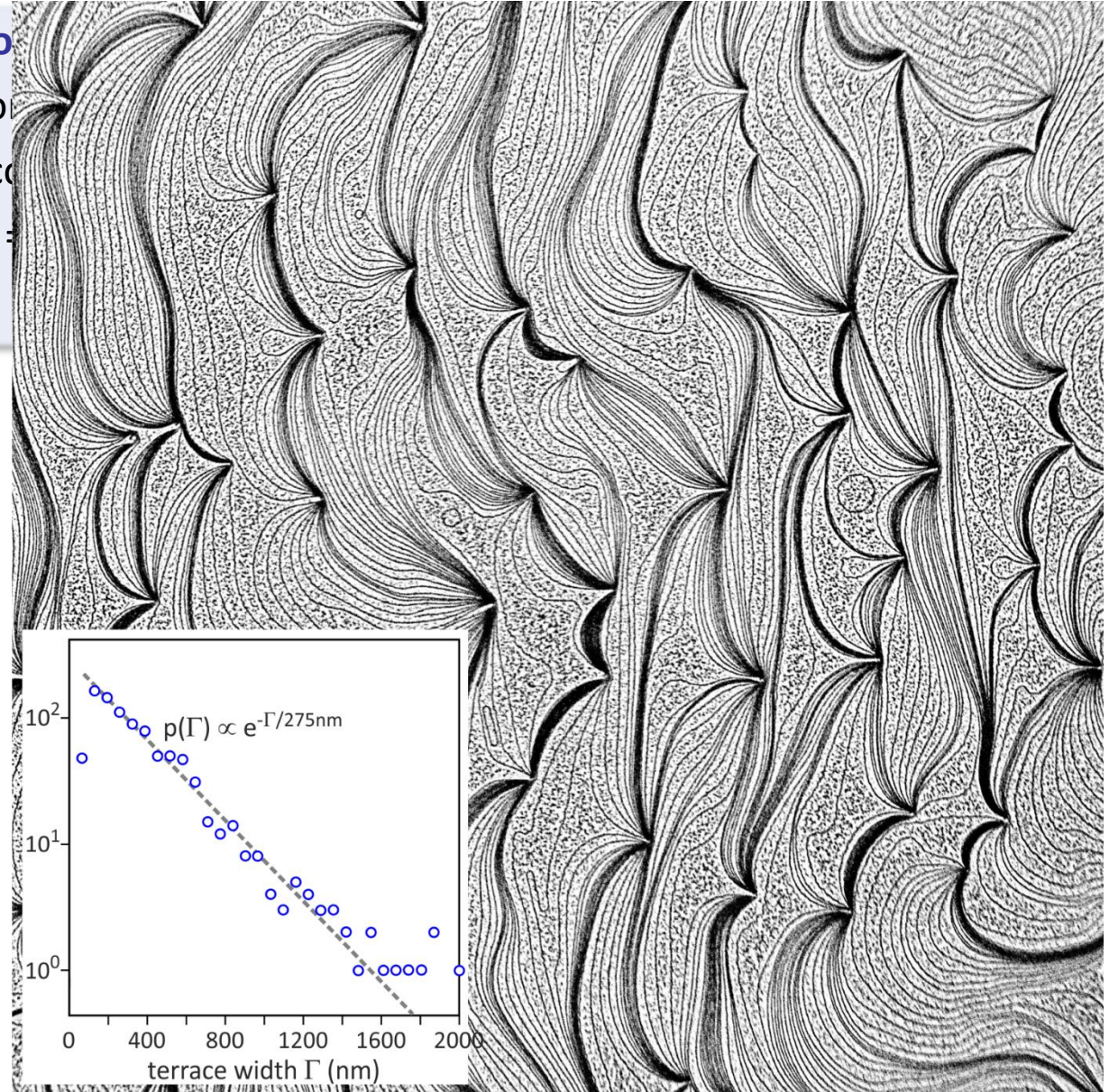


Steps acting as seeds

Extreme slow recovery of growth

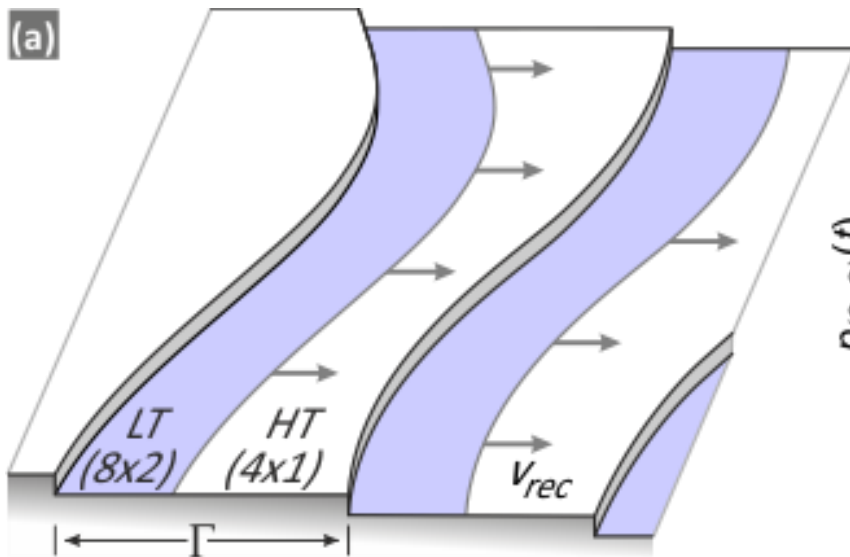
- Improved vacuum conditions
- Step edges trigger recovery
- Use step morphology = 1-dim. recovery front

PEEM - micrograph
Si(111) - 0.08°
FoV = 50 μm
$\langle \Gamma \rangle = 340 \text{ nm}$

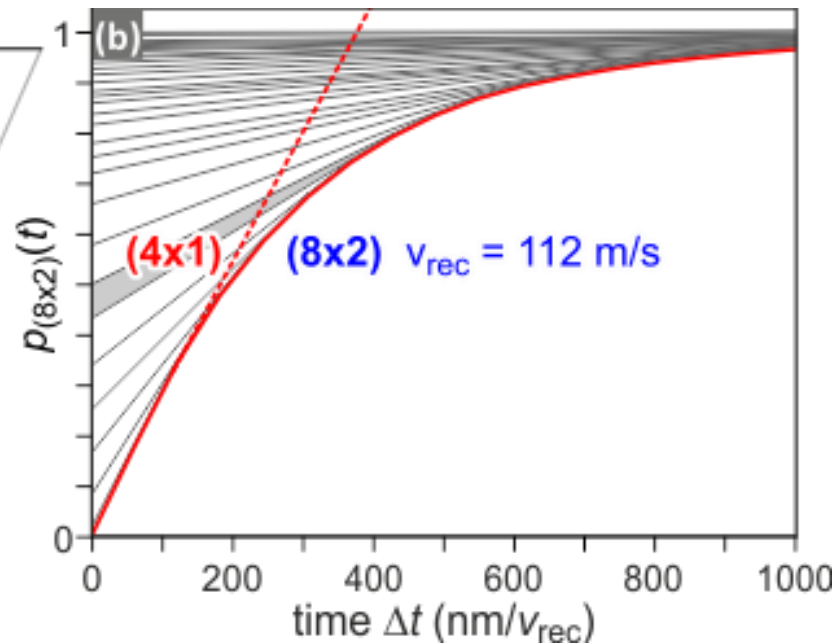


Extreme slow recovery of ground state

- Improved vacuum conditions - adsorbates acting as seed are not present
- Step edges trigger recovery of (8x2) ground state
- Use step morphology => determine velocity of 1-dim. recovery front through $v_{8x2} = s / t$



$$v_{8x2} = 340 \text{ nm} / 3 \text{ ns} = 112 \text{ m/s}$$





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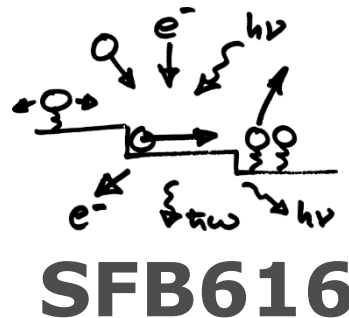
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Si(111)-In(8x2) \leftrightarrow (4x1)

System with Peierls instability

1st order phase transition at 130 K

Non-equilibrium dynamics of structural transition

- ultrafast photo excitation of phase transition in 350 fs
- accelerated displacive transition
- critical damping
- delayed thermal excitation of surface atoms at 7 ps
- formation of a supercooled, metastable surface phase
- speed of recovery ~ 100 m/s

